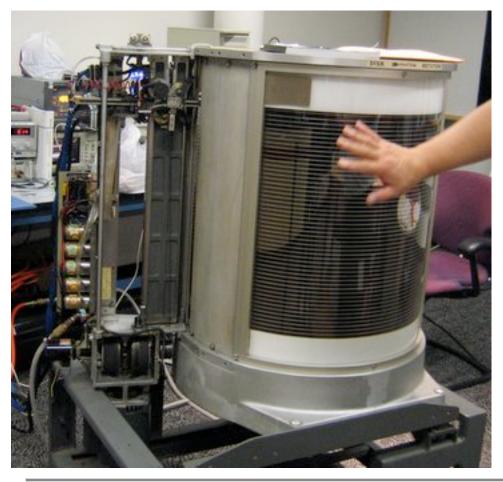
#### **Project:**

Your project will be to assess the prospects of a future information storage or memory technology.

Some possible technologies to consider (choose one):

Ferroelectric Random Access Memory Optical Storage Holographic Storage Flash Memory Phase Change Memory (PC-RAM) Resistive Random Access Memory Probe Based Storage Devices Molecular Memory Devices

## Introduction to Magnetic Recording



ph587

P. LeClair 26 Jan 2009

IBM 350 RAMAC, the first hard disk

it stored about 4.4Mb

wikipedia.org - "RAMAC"

#### THE UNIVERSITY OF ALABAMA

## what do I mean by magnetic recording?

## what do I mean by magnetic recording?



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## what do I mean by magnetic recording?

hard disks.

### only hard disks.



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## why do we use hard disks?

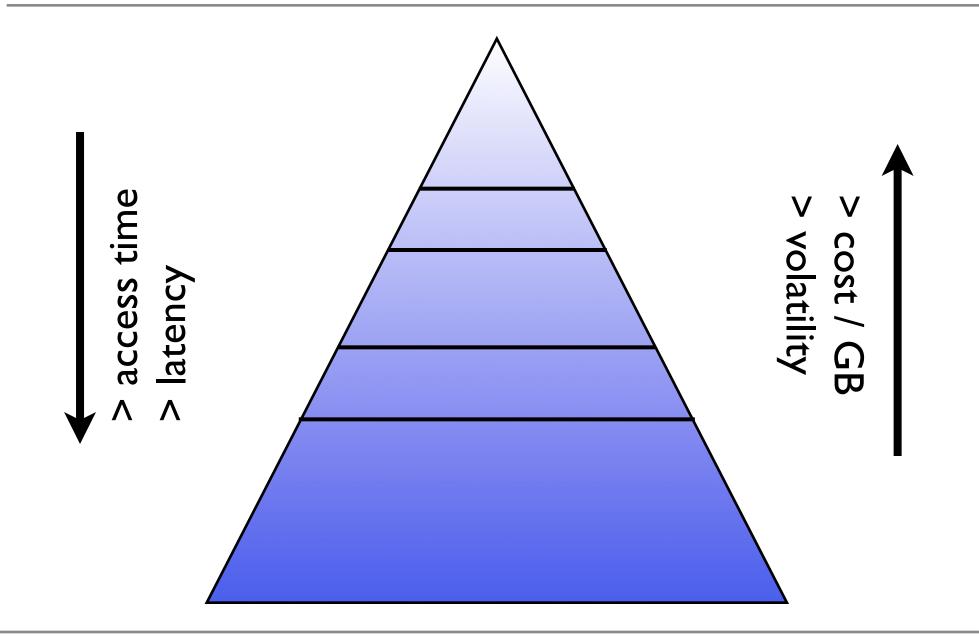
### what is their role in a computer?

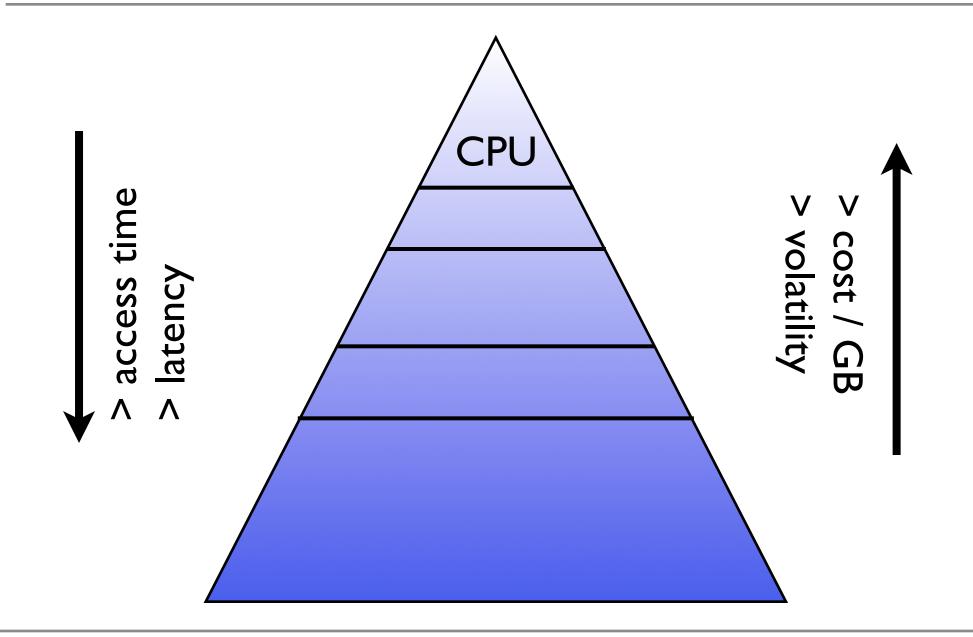
### benefits?

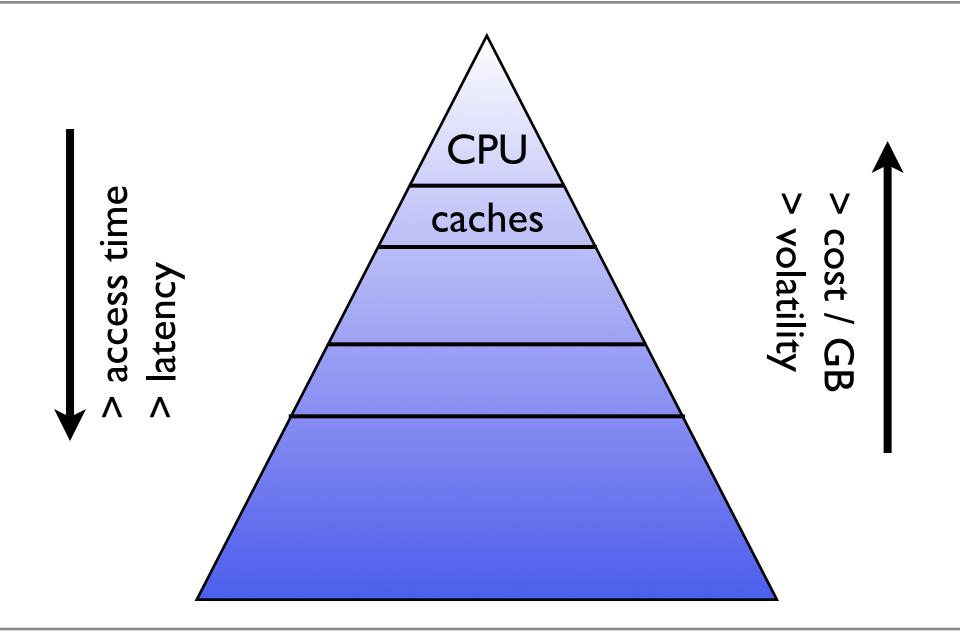
### disadvantages?

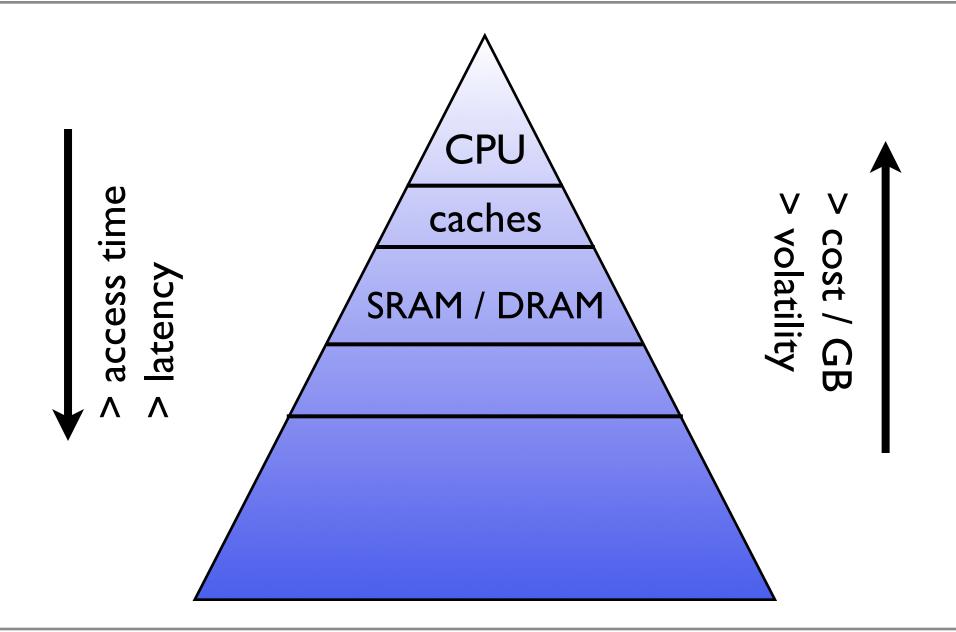


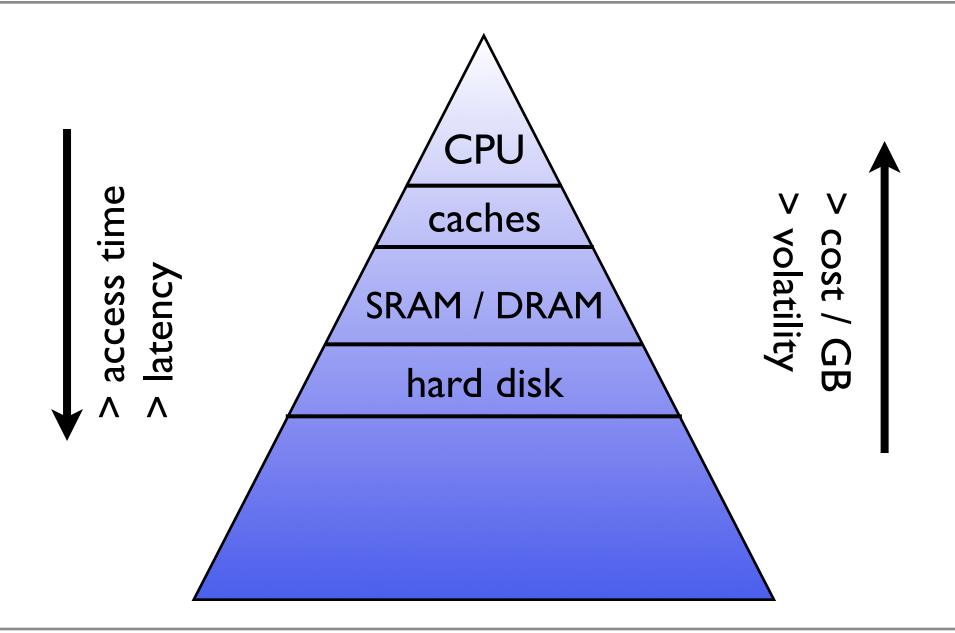
and the real reason .. \$\$\$

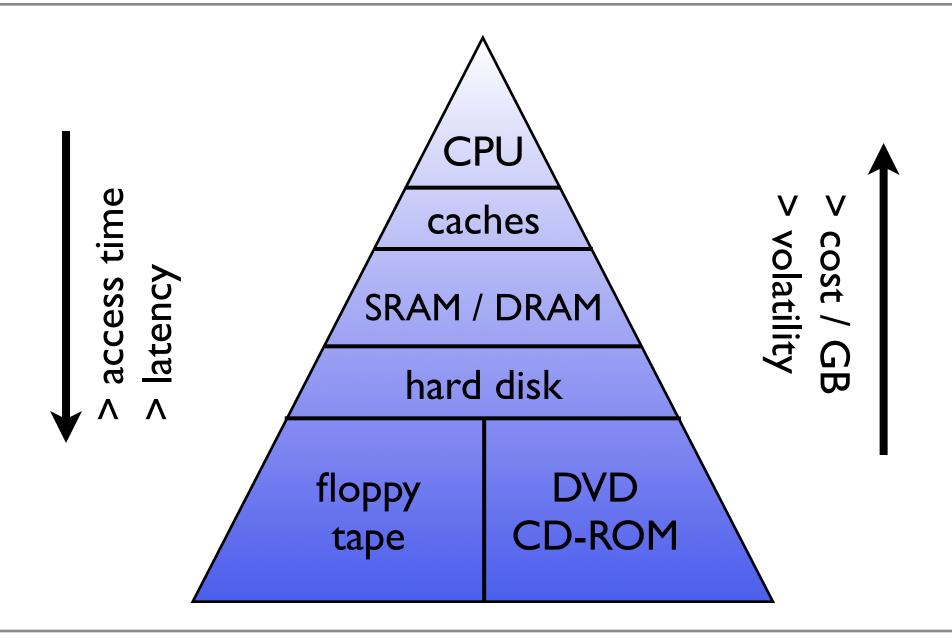


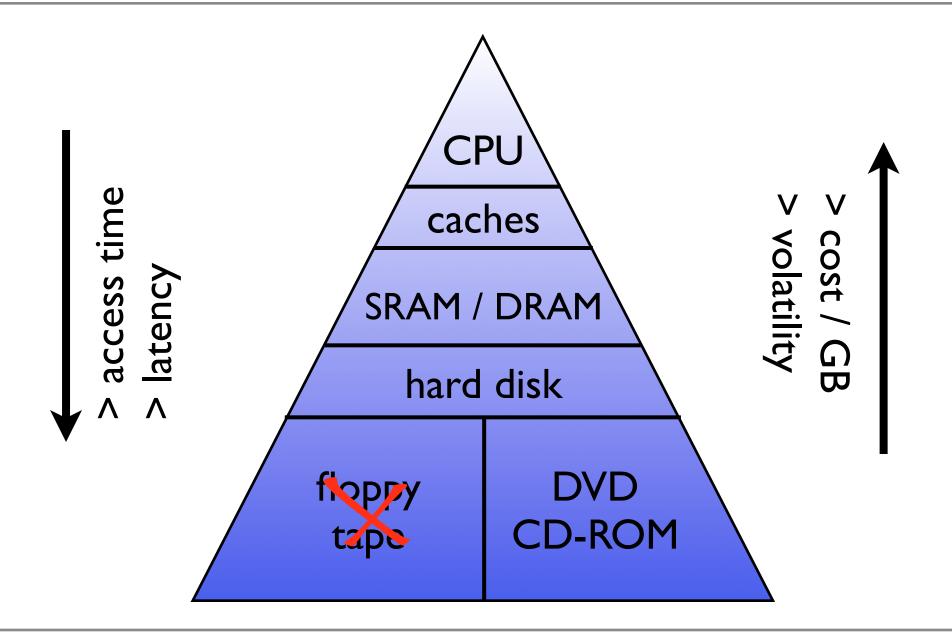


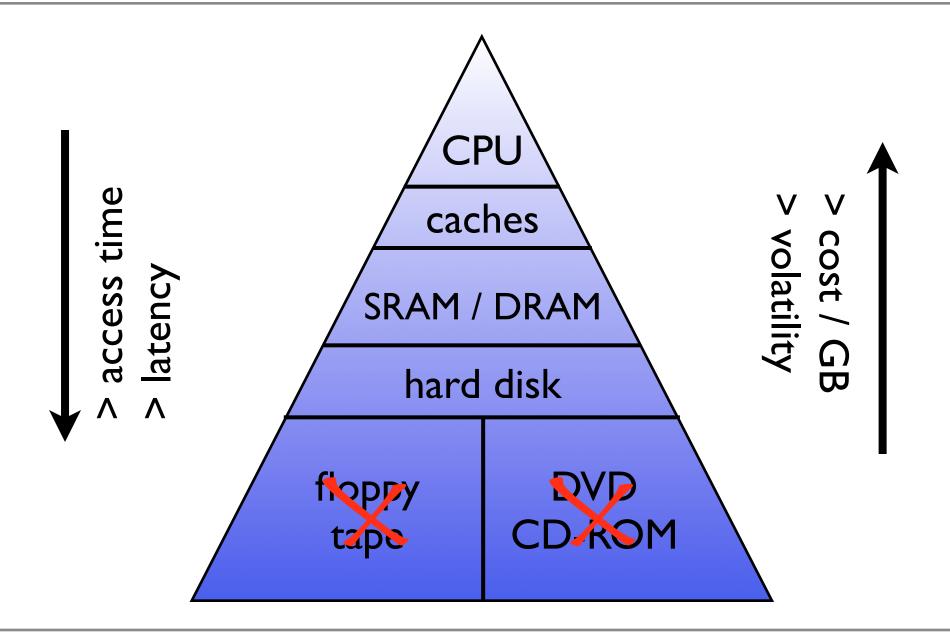












## terminology

### RAM

random access memory

ROM

read-only memory

### access time & latency?

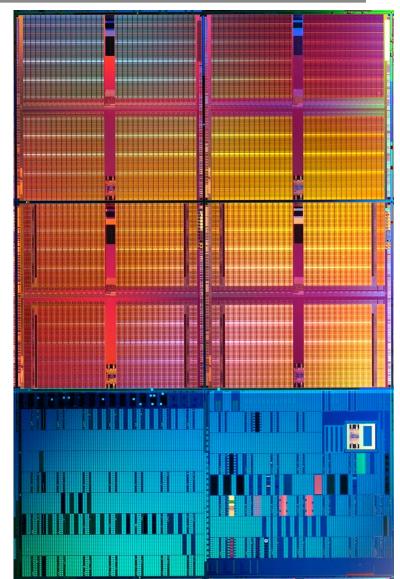
time between request for info & info returned

### \$ / GB

primary figure of merit. most other things can be worked around

### nonvolatility?

retains data without power



45nm SRAM die intel.com

## every bit has a role

### cache - reduce latency to main memory

small memories close to CPU even faster than main memory temp storage of frequently accessed items

### SRAM / DRAM - main memory

blazingly fast relatively large voltaile!!

### HDD - mass storage

higher latency enormous capacity nonvolatile

### removable

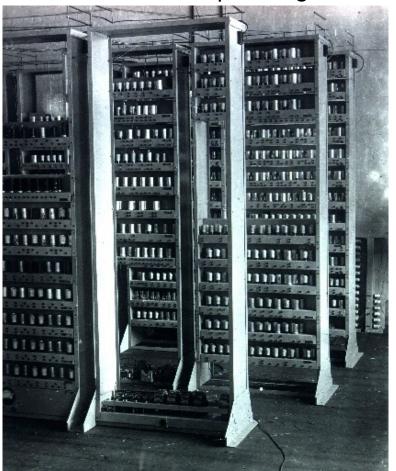
portability

backup

large ROM

future paradigm shifts? distributed net storage?

#### EDSAC / wikipedia.org



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## the need for hard disks (tech)

### volatility of semiconductor memories!

some sort of nonvolatile storage necessary why not just battery backup of SRAM?

### cost per GB

SRAM/DRAM are too expensive Flash is too expensive cache RAM is more expensive

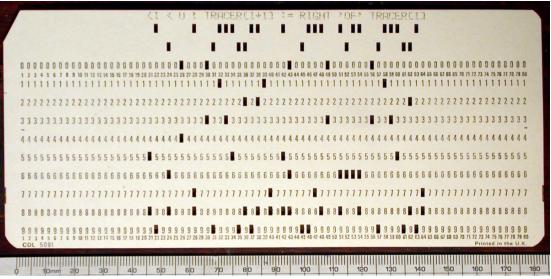
### size & throughput

higher latency, but bandwidth is huge enormous sizes

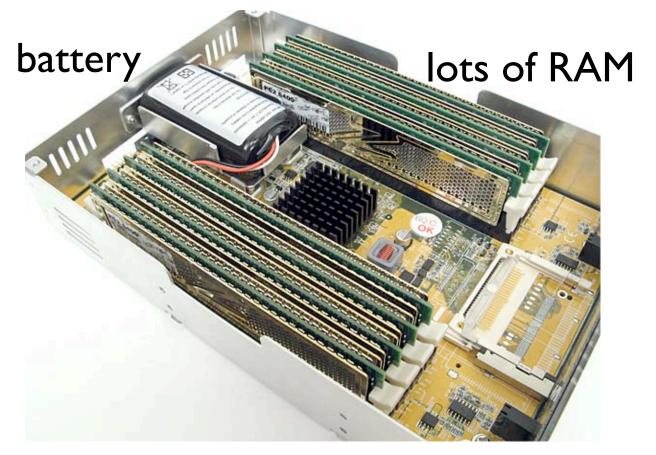
### endurance

essentially unlimited cycling radiation hard

#### punched cards are nonvolatile



Sometimes, we would trick the system into using RAM as a disk to avoid swapping floppies.



### now RAM disks make a comeback ...

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## the need for mass storage (human)

### sound

several MB per minute / lossy tens of MB per minute / "lossless"

### pictures

several MB per image

### video

~ I MB per sec several GB per movie with lossy compression!

data mining enormous sizes



apple.com

### THE UNIVERSITY OF ALABAMA

## how do hard disks work, more or less?



wikipedia.org - "Hard\_Disk"

### spinning (~10<sup>4</sup> rpm) part holds data. sliding part reads and writes data.



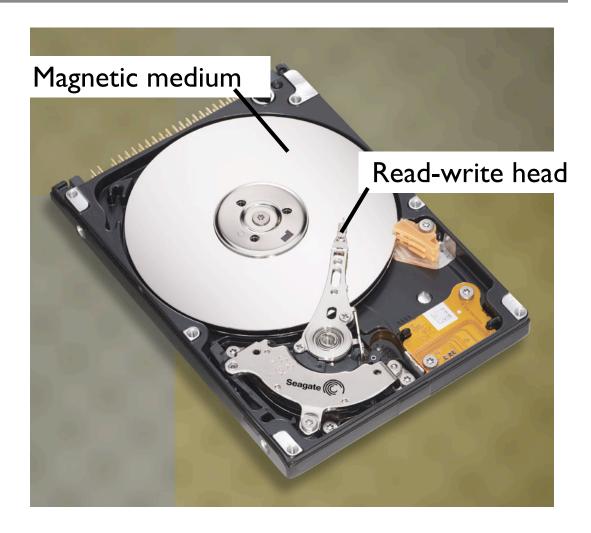
160 Gbit 2.5" perpendicular drive for laptops

images from M. Coey



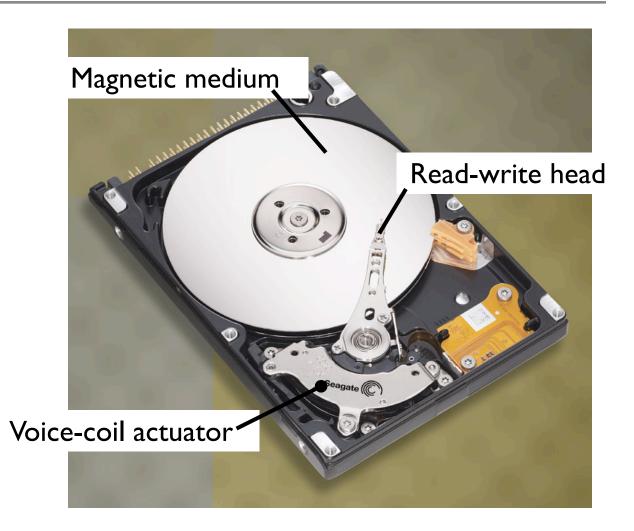
160 Gbit 2.5" perpendicular drive for laptops

images from M. Coey



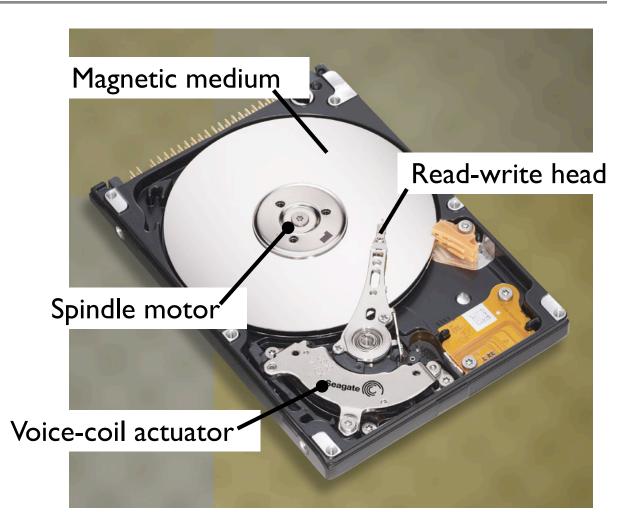
160 Gbit 2.5" perpendicular drive for laptops

images from M. Coey



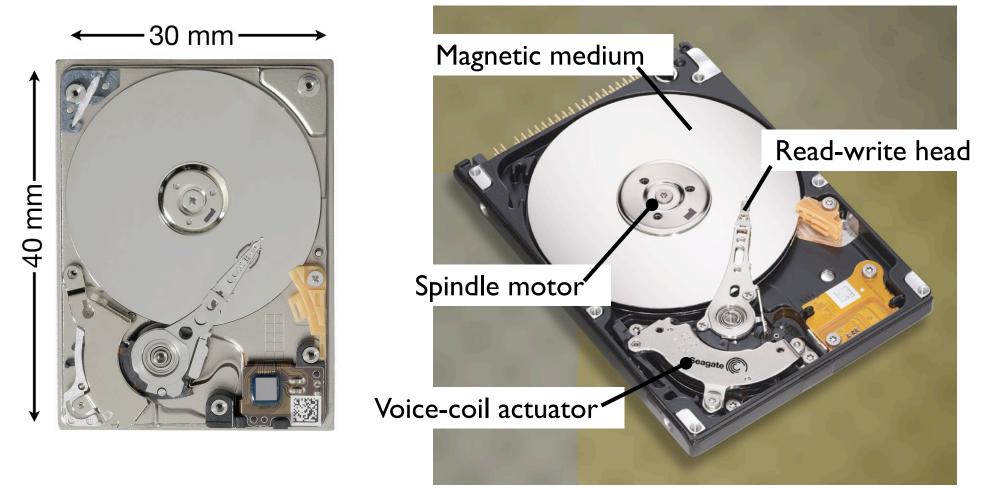
#### 160 Gbit 2.5" perpendicular drive for laptops

images from M. Coey



#### 160 Gbit 2.5" perpendicular drive for laptops

images from M. Coey

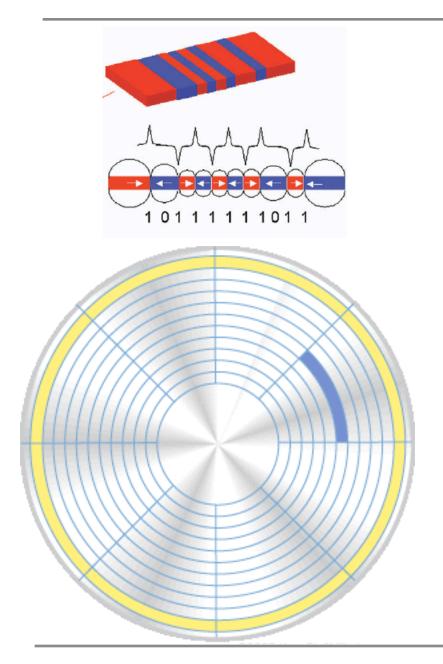


8 Gbit 1" drive for cameras

160 Gbit 2.5" perpendicular drive for laptops

images from M. Coey

## media basics



Hard disk tiny magnetized regions direction (N/S) stores bit magnetic sensor reads bits

LP records tiny bumps needle moves

pits store bits

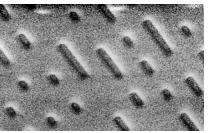
optical reflectivity

**CDs** 

actual record grooves



actual CD surface



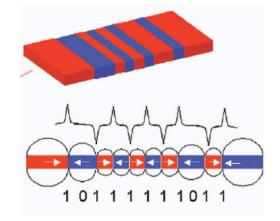
## media basics

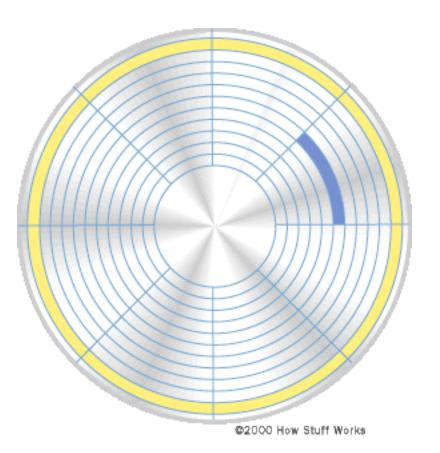
hard disk platters are round.

so how is data arranged?

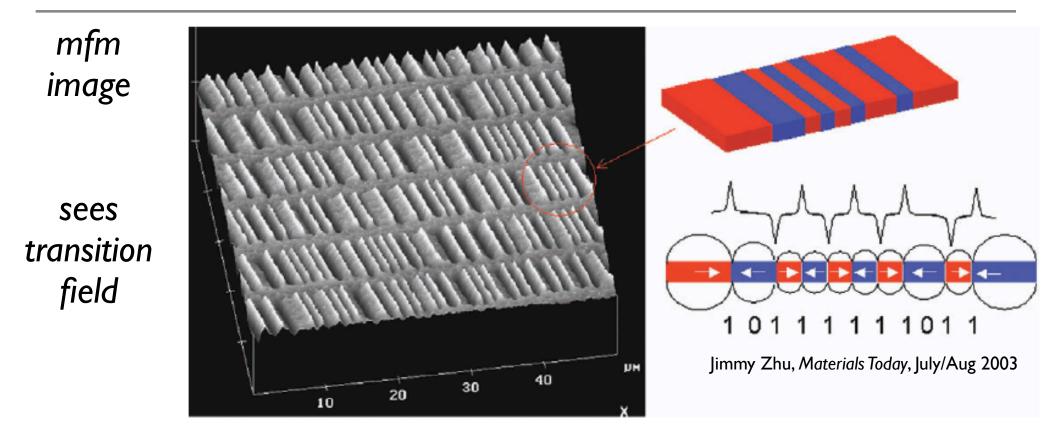
tracks = concentric circles
sectors = wedge of a track

sector has fixed # bytes





## media basics



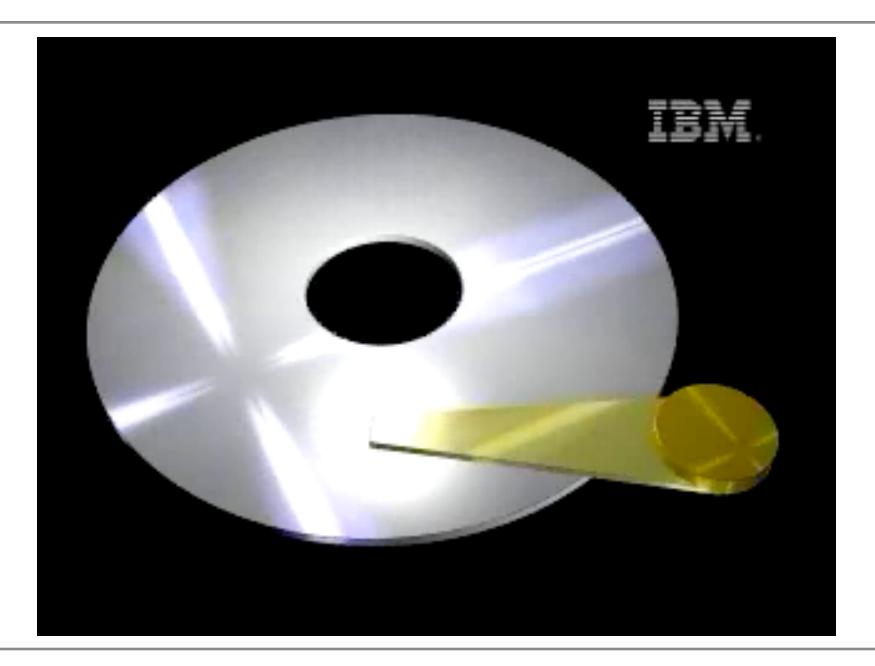
CoCrPt alloy

platters - Al or glass substrate

typical magnetic region

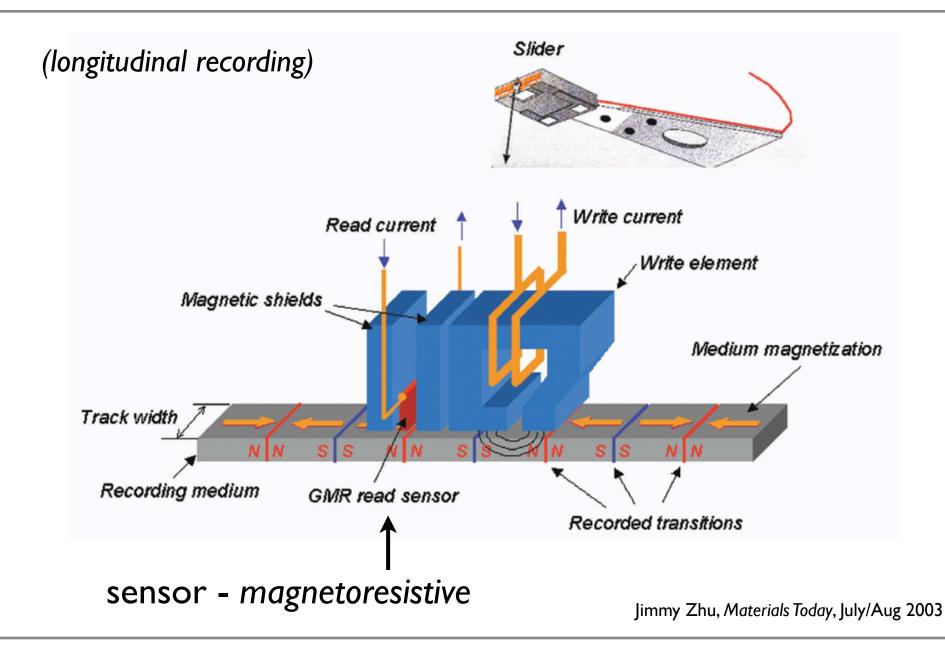
~200-250 nm wide, ~25-30 nm down-track

100 billion bits (Gigabits) per in<sup>2</sup>



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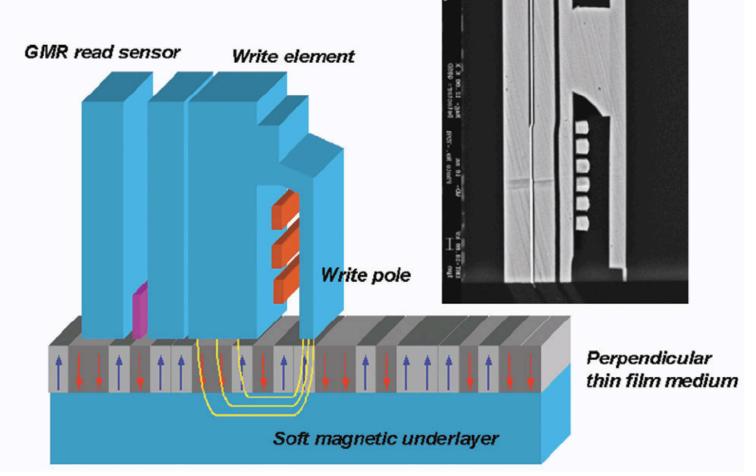
## reading and writing basics



## reading and writing basics

### (perpendicular recording)

Jimmy Zhu, Materials Today, July/Aug 2003



soft underlayer becomes part of the flux guide ... careful concentration of flux ...

## read head (and its reflection)



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## positioning basics

- current powers voice coil<sup>†</sup>
- field generated moves head L or R
- more precise than stepper motor



<sup>†</sup> this is the same way a speaker cone moves

## positioning basics

- current powers voice coil<sup>†</sup>
- field generated moves head L or R
- more precise than stepper motor



IBM 62PC "Piccolo" HDD, ~1979 - an early 8" disk



wikipedia.org - "Hard\_Disk"

<sup>†</sup> this is the same way a speaker cone moves

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why magnets?

microscopic view

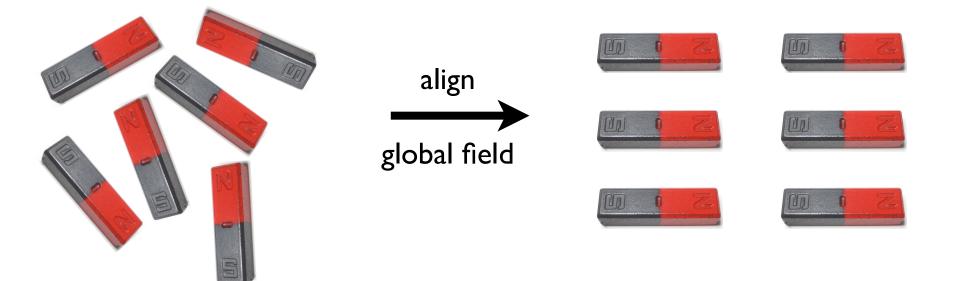


### magnets remember their state once magnetized, they stay that way

# with a little bit of energy, we can control them switch from N to S

# why magnets?

microscopic view



## magnets remember their state once magnetized, they stay that way

# with a little bit of energy, we can control them switch from N to S

why magnets?

microscopic view



## magnets remember their state once magnetized, they stay that way

# with a little bit of energy, we can control them switch from N to S

# why magnets?



## magnets remember their state once magnetized, they stay that way

# with a little bit of energy, we can control them switch from N to S

# why magnets?

what happens when you break a magnet?

## you get two magnets

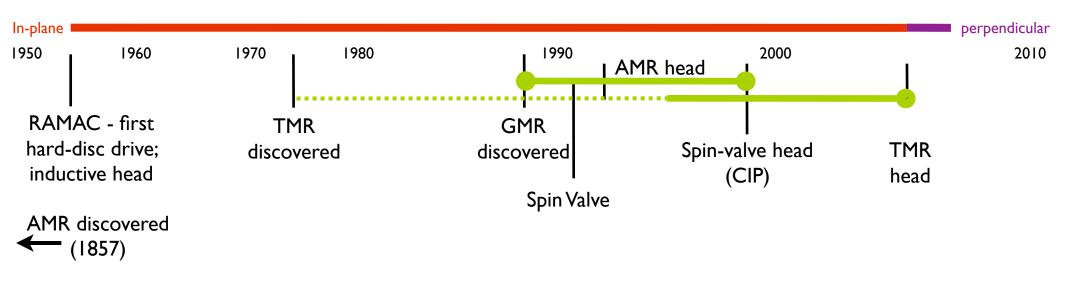


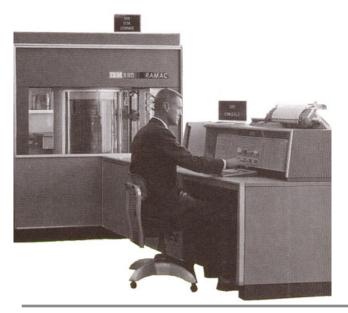


## now: do this 25 more times

# 33 million magnets, all 50nm across about 1,000 times thinner than a hair we can make really tiny magnets smaller is better, to a point

# technology timeline





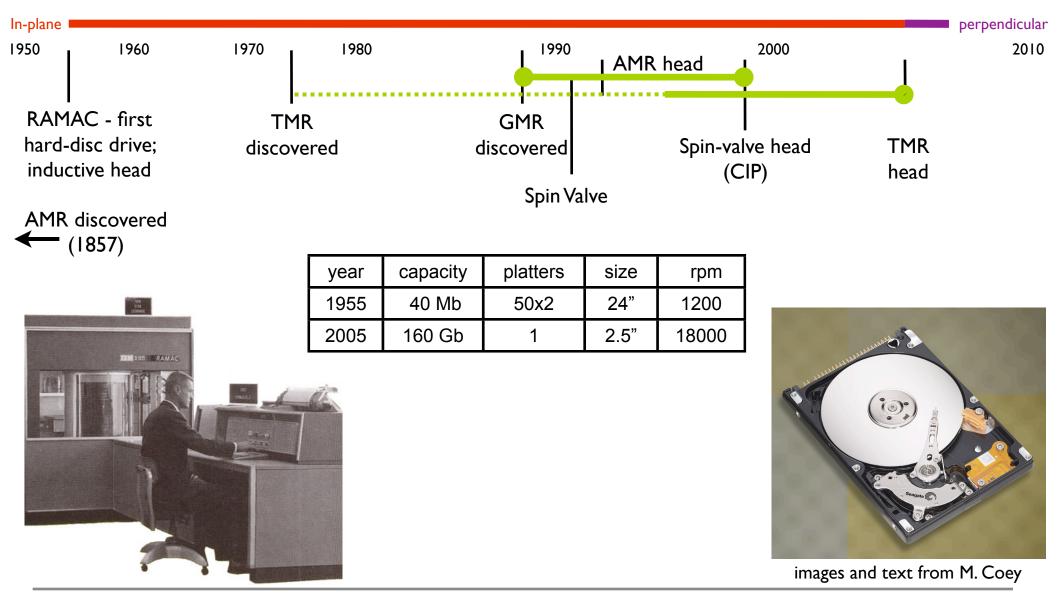


#### images and text from M. Coey

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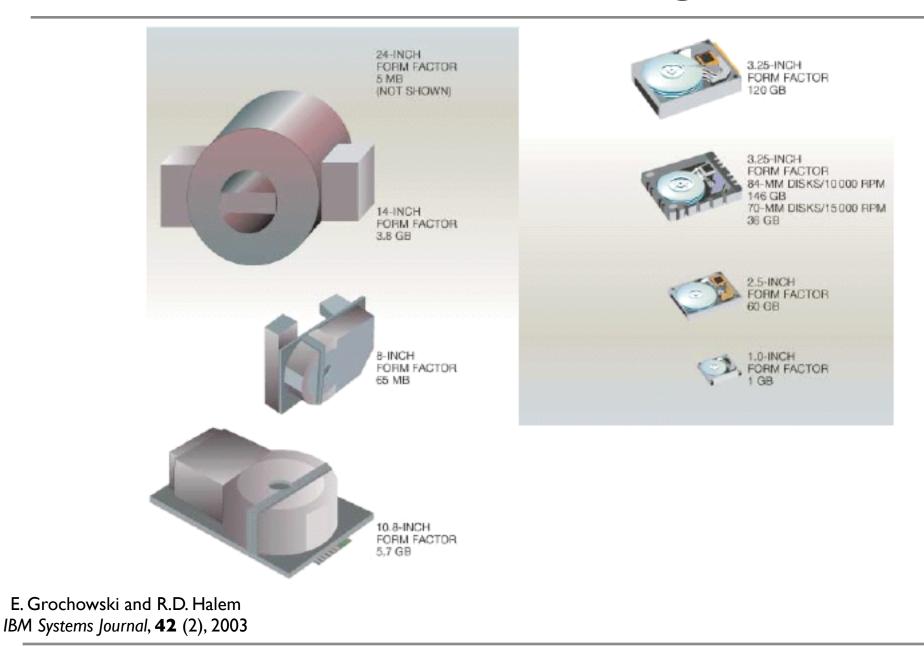
# technology timeline



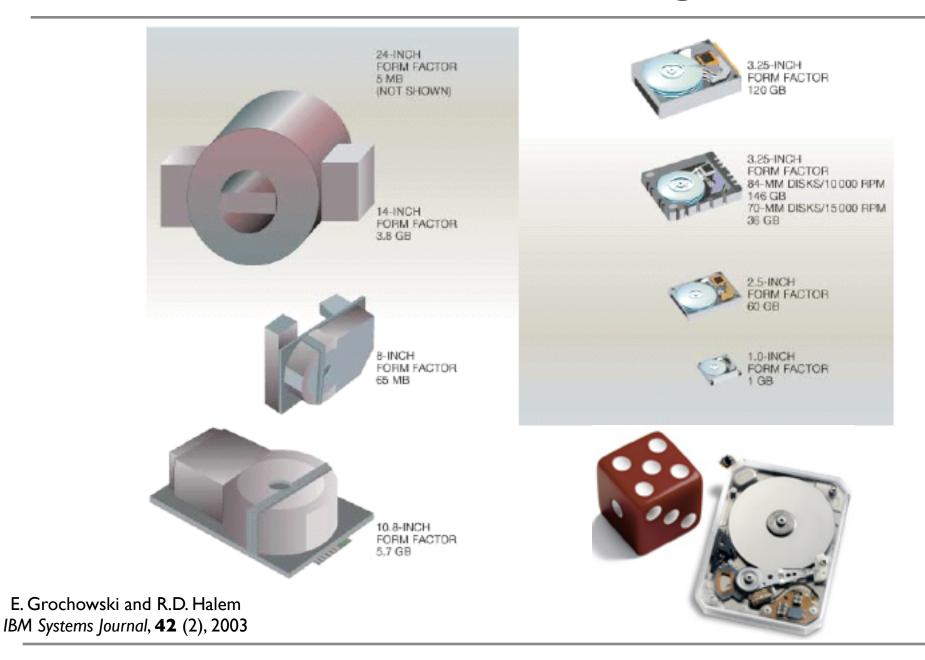
#### THE UNIVERSITY OF ALABAMA

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# the incredible shrinking hard disk



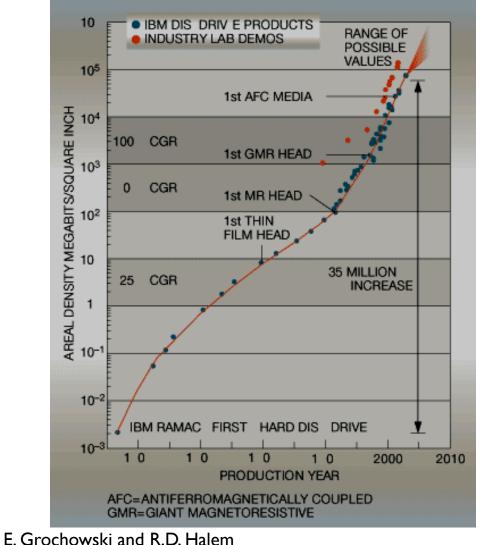
# the incredible shrinking hard disk



## growth of areal density

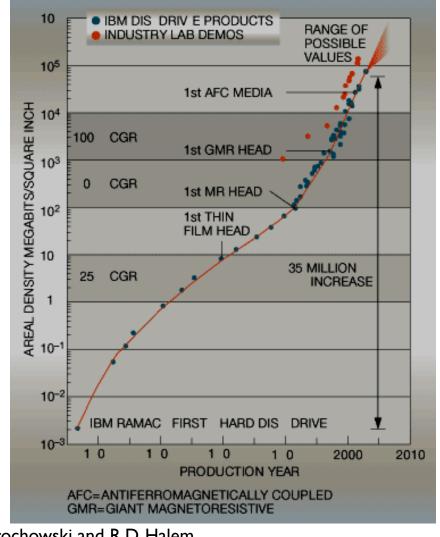
E. Grochowski and R.D. Halem IBM Systems Journal, **42** (2), 2003

## growth of areal density



IBM Systems Journal, **42** (2), 2003

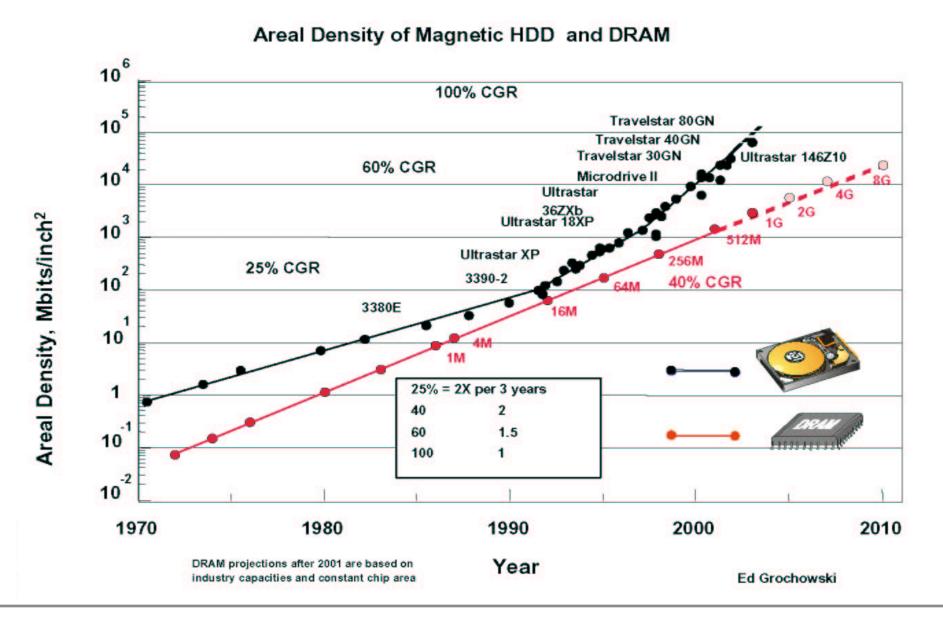
# growth of areal density



104 RANGE OF RAW CAPACITY PER FLOOR SPACE AREA, GBYTES/SQUARE FOOT POSSIBLE VALUES 103 IBM ESS MOD 800 ESS MOD F  $10^{2}$ 60% CGR RAMAC 2 101 100 25% CGR 3380 10-1 10-2 10-3 IBM RAMAC (FIRST HARD DISK DRIVE) 10-1960 1970 1980 1990 2000 2010 PRODUCTION YEAR ESS=IBM TOTALSTORAGE™ ENTERPRISE STORAGE SERVER™

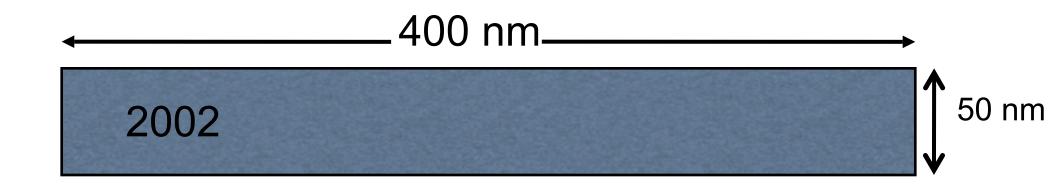
E. Grochowski and R.D. Halem IBM Systems Journal, **42** (2), 2003

## areal density vs. DRAM



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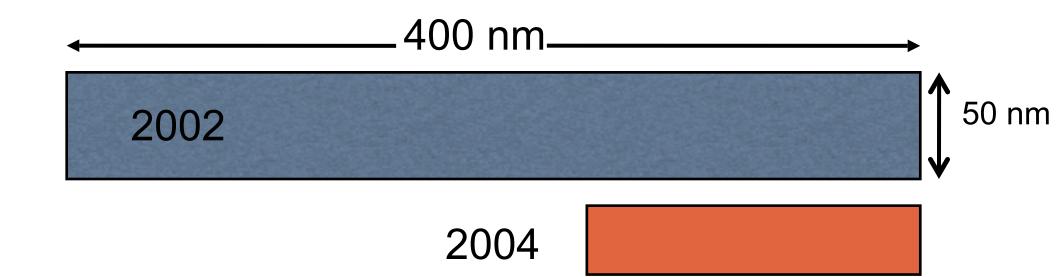
CENTER FOR MATERIALS FOR INFORMATION TECHNOLOGY An NSF Science and Engineering Center



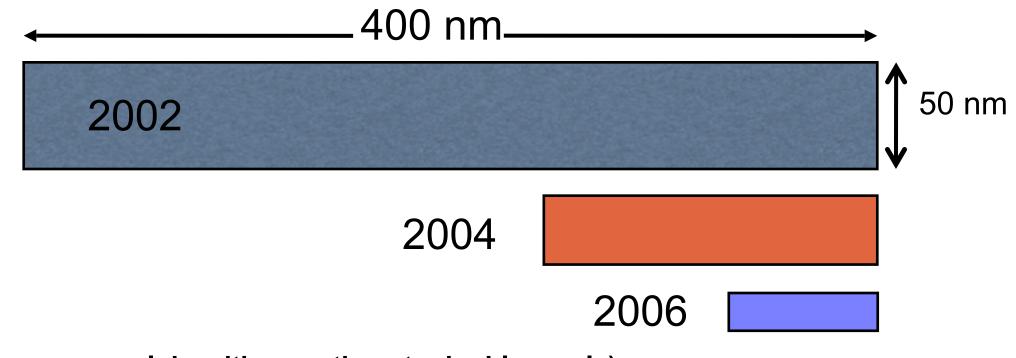
(assumes areal densities continue to double yearly)

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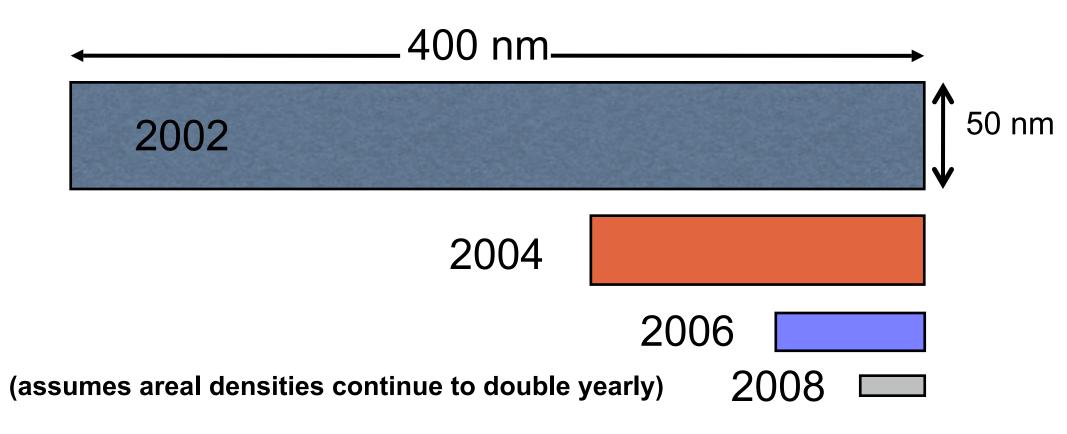
CENTER FOR MATERIALS FOR INFORMATION TECHNOLOGY An NSF Science and Engineering Center

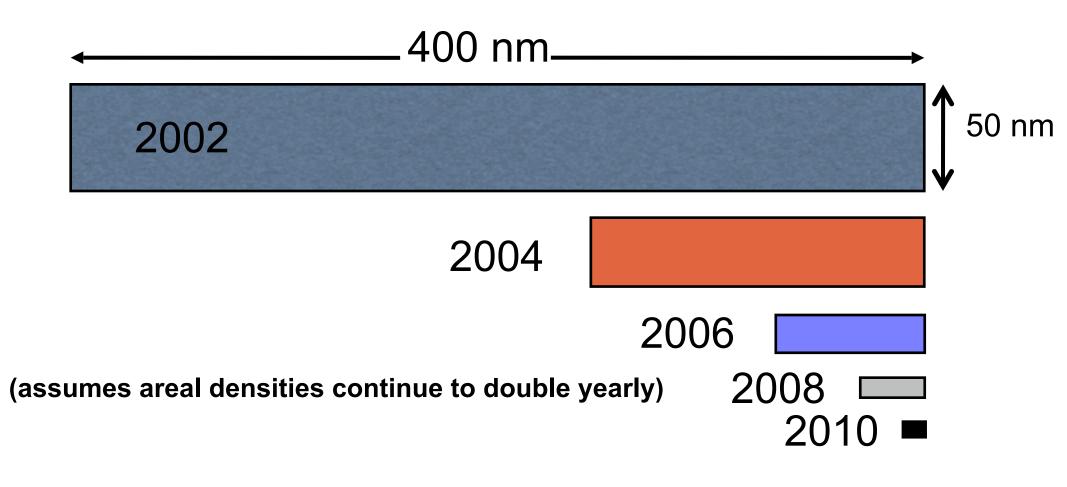


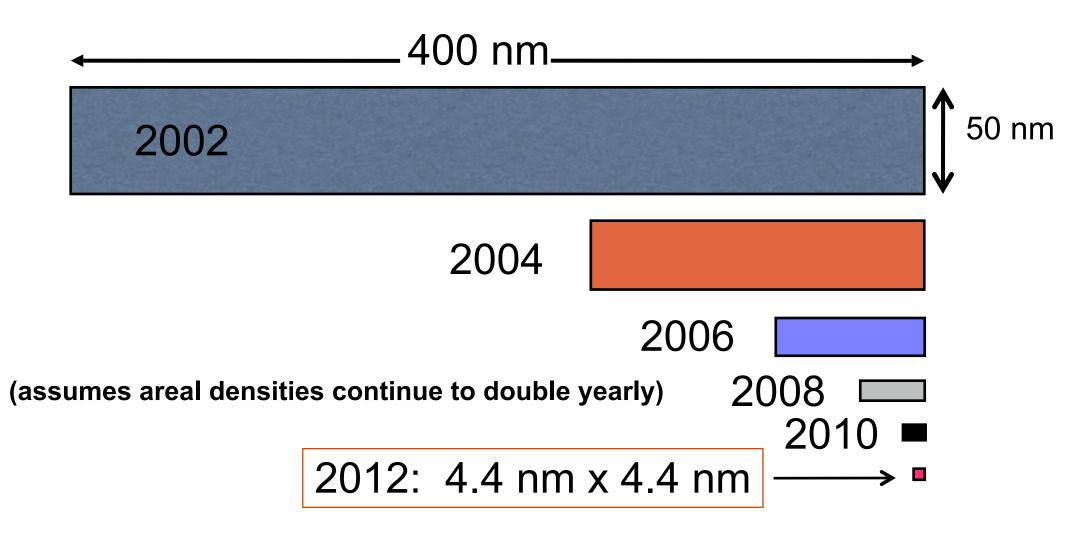
#### (assumes areal densities continue to double yearly)

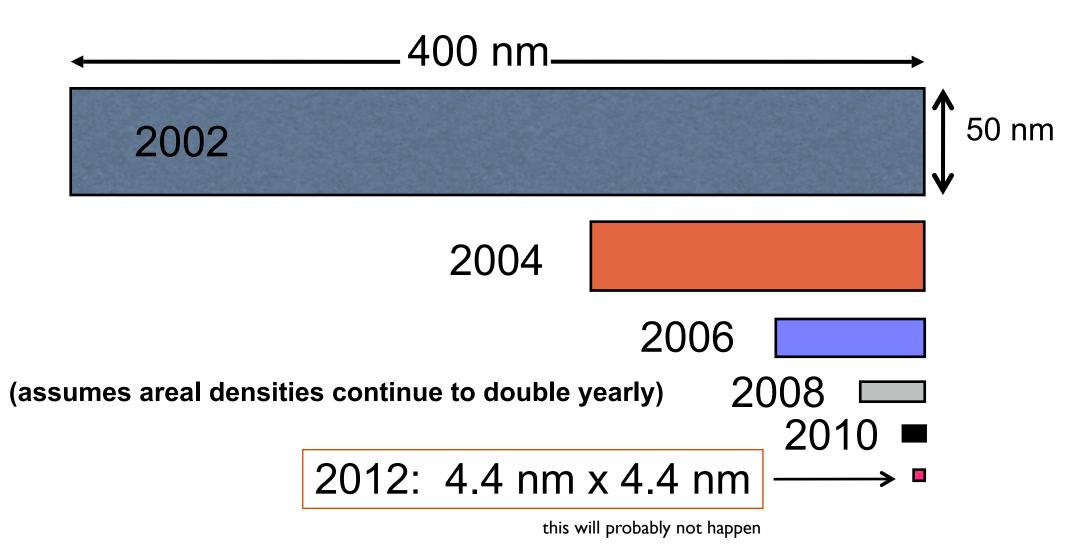


(assumes areal densities continue to double yearly)









## 50 TB per square inch on a quarter ...

- over 3.4 million high-resolution photos, or ...
- 2,800 audio CDs, or...
- 1,600 hours of television, or ...

## 50 TB per square inch on a quarter ...

- over 3.4 million high-resolution photos, or ...
- 2,800 audio CDs, or...
- 1,600 hours of television, or ...
- the entire printed collection of the U.S.
   Library of Congress



Library of Congress, Jefferson building

## so what's the problem?

at some point, they are no longer stable

heat makes them 'wiggle' like drops of water on a griddle

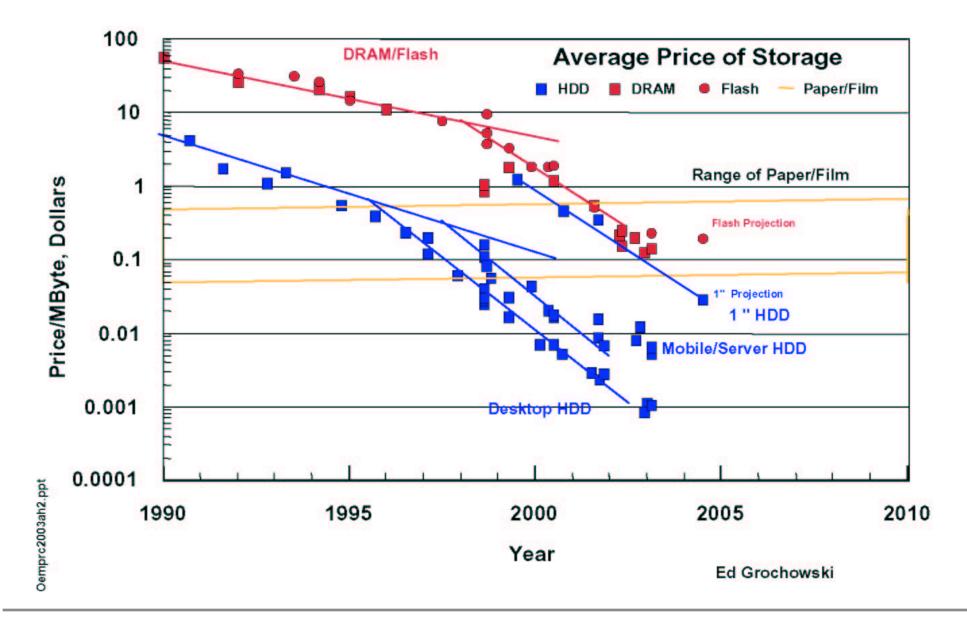
bits are no longer reliable

so we need stronger magnets ... ... which need more field to magnetize ... which needs more power

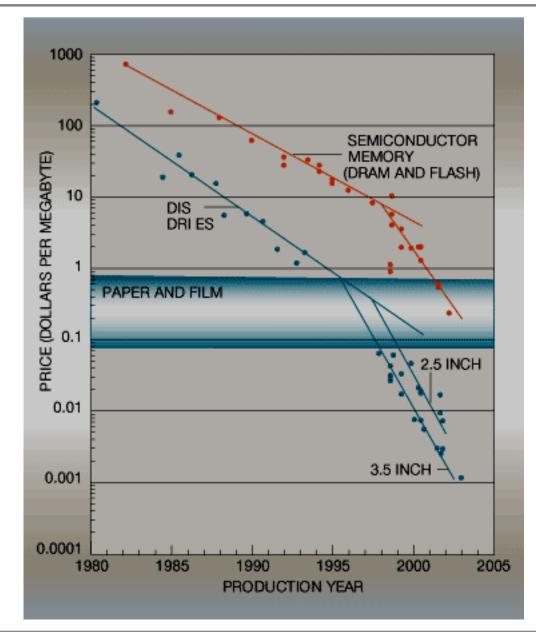
HUGE challenge in nanoscale materials science!



## \$\$\$ vs flash and DRAM

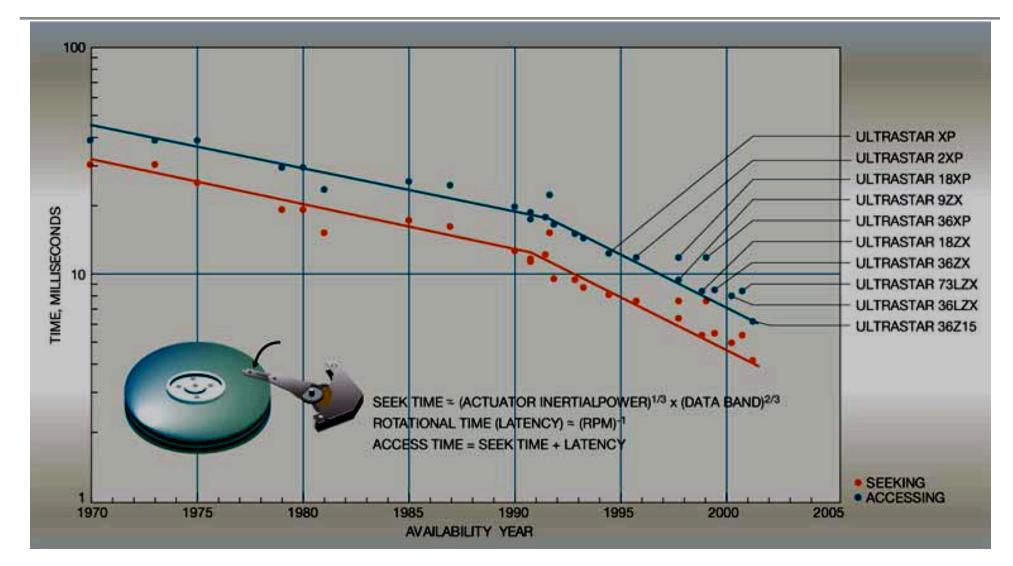


## \$\$\$ vs flash and DRAM



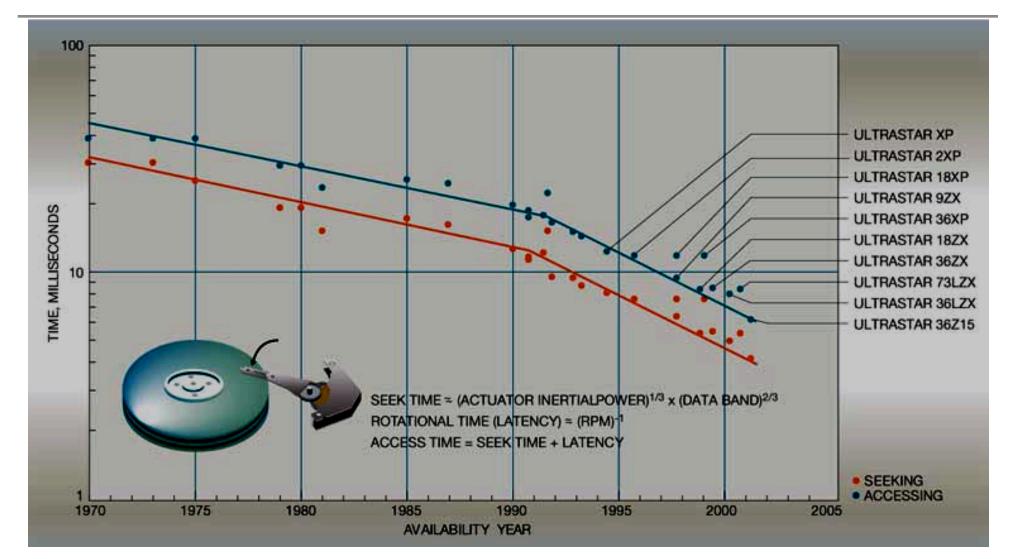
E. Grochowski and R.D. Halem IBM Systems Journal, **42** (2), 2003

## seek time



E. Grochowski and R.D. Halem IBM Systems Journal, **42** (2), 2003

## seek time

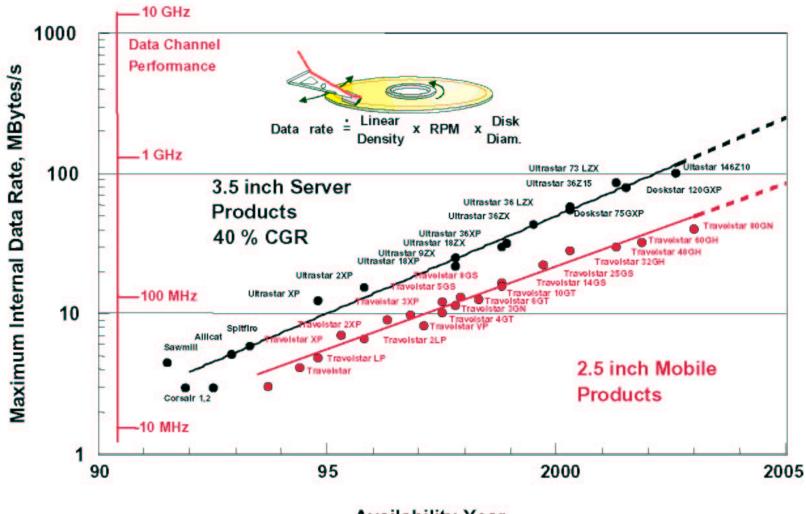


# far higher than DRAM/SRAM (~nsec) reduction limited by mechanics!

#### E. Grochowski and R.D. Halem IBM Systems Journal, **42** (2), 2003

# throughput

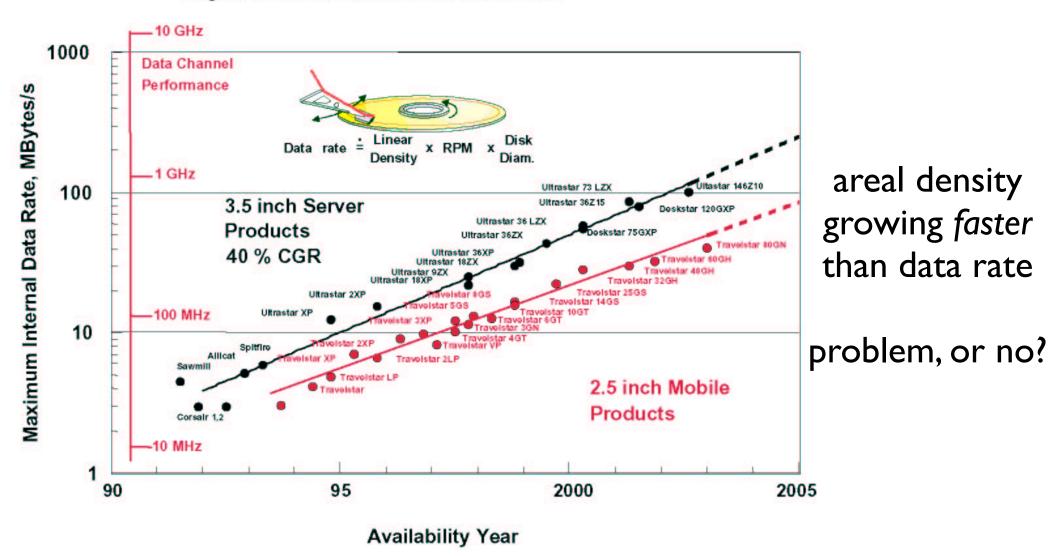
Magnetic Hard Disk Drive Internal Data Rate



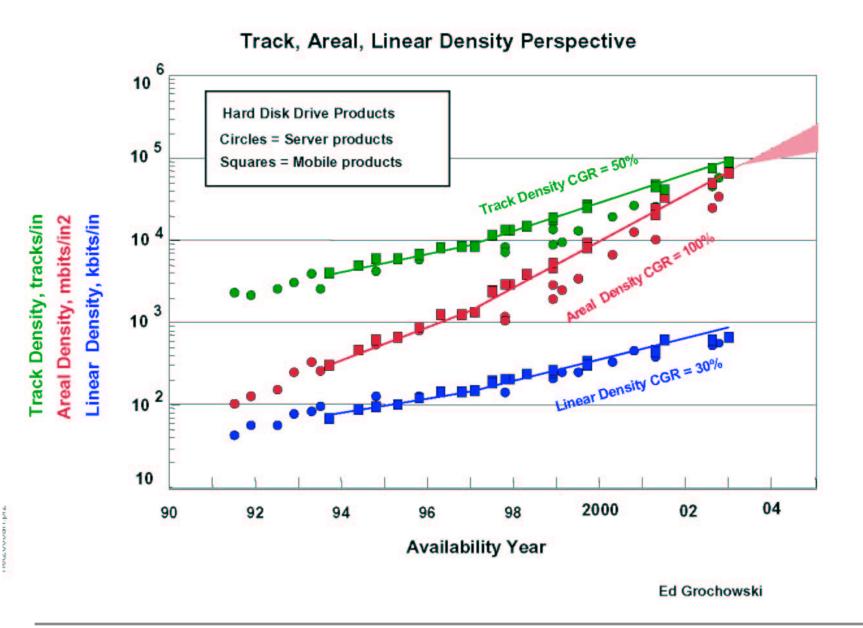
**Availability Year** 

# throughput

Magnetic Hard Disk Drive Internal Data Rate



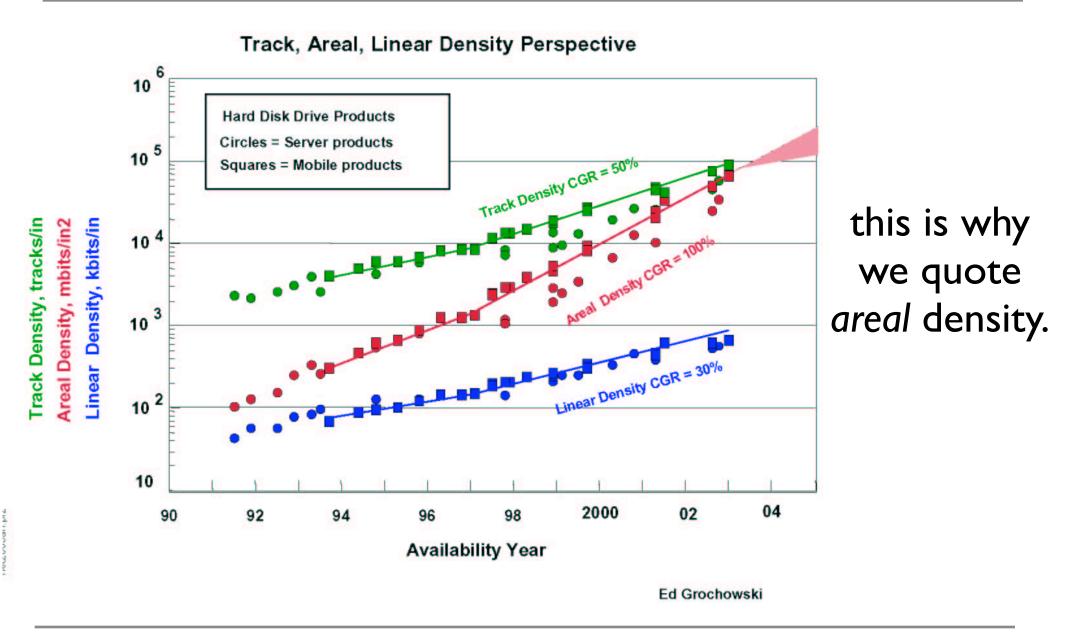
## density metrics



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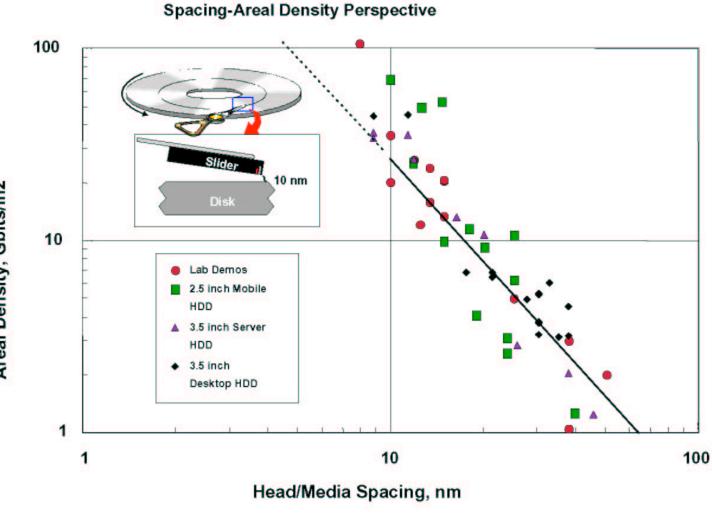
CENTER FOR MATERIALS FOR INFORMATION TECHNOLOGY An NSF Science and Engineering Center

## density metrics



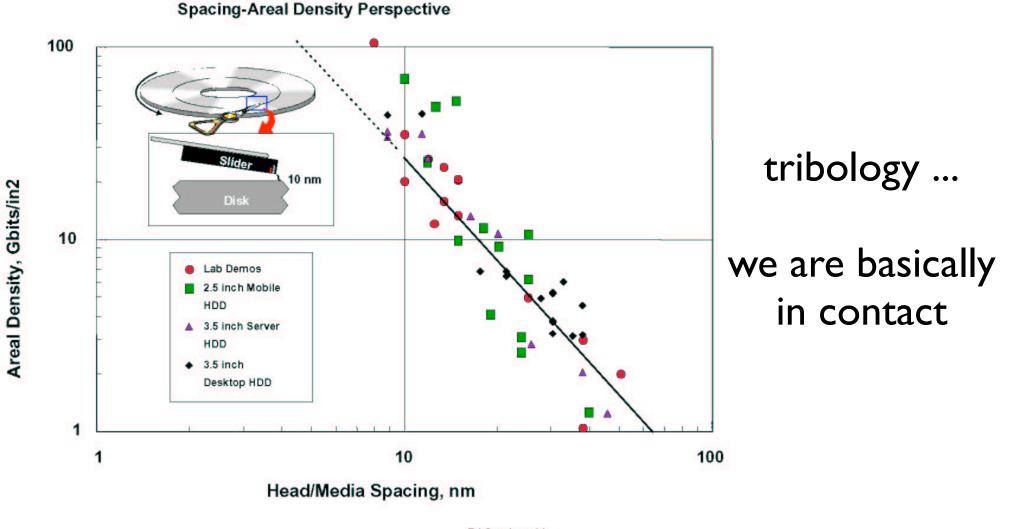
## head-media spacing

Ed Grochowski



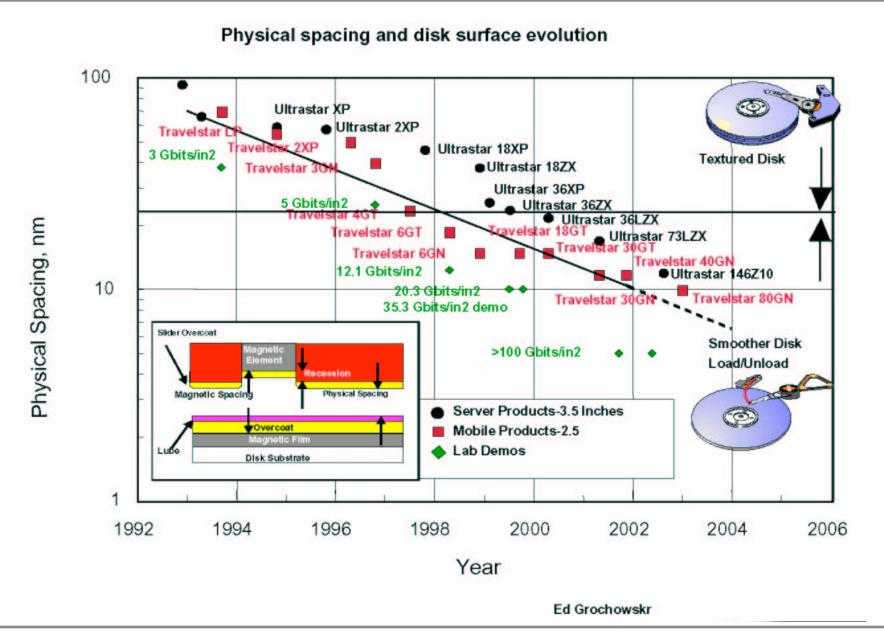
Areal Density, Gbits/in2

## head-media spacing



Ed Grochowski

# physical spacing



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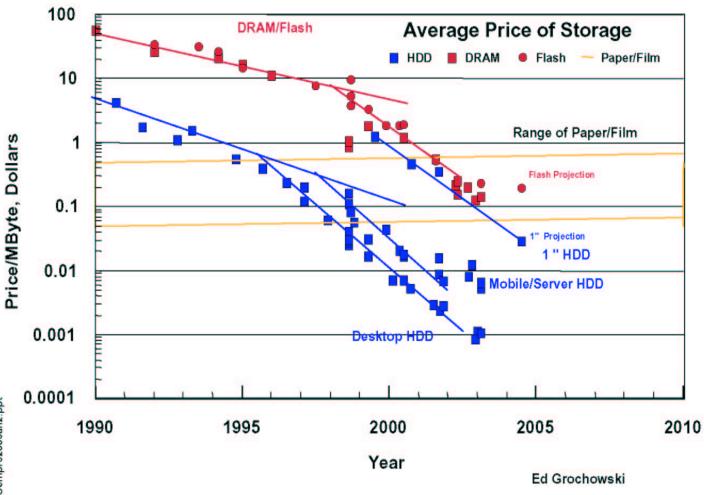
# competition?

	SRAM	DRAM	Flash	FeRAM	MRAM	PCRAM
Read speed	Fastest	Medium	Fast	Fast	Fast	Fast
Write speed	Fastest	Medium	Slow	Medium	Fast	Medium
Array efficiency	High	High	Medium/low	Medium	Medium/high	Medium/high
Future scalability	Good	Limited	Limited	Limited	Good	Good
Cell density	Low	High	High	Medium	Medium/high	Medium/higł
Nonvolatility	No	No	Yes	Yes	Yes	Yes
Endurance	Infinite	Infinite	Limited	Limited	Infinite	Infinite
Cell leakage	Increasing	High	Low	Low	Low	Low
Low voltage	Yes	Limited	Limited	Limited	Yes	Yes
Complexity	Low	Medium	Medium	Medium	Medium	Medium

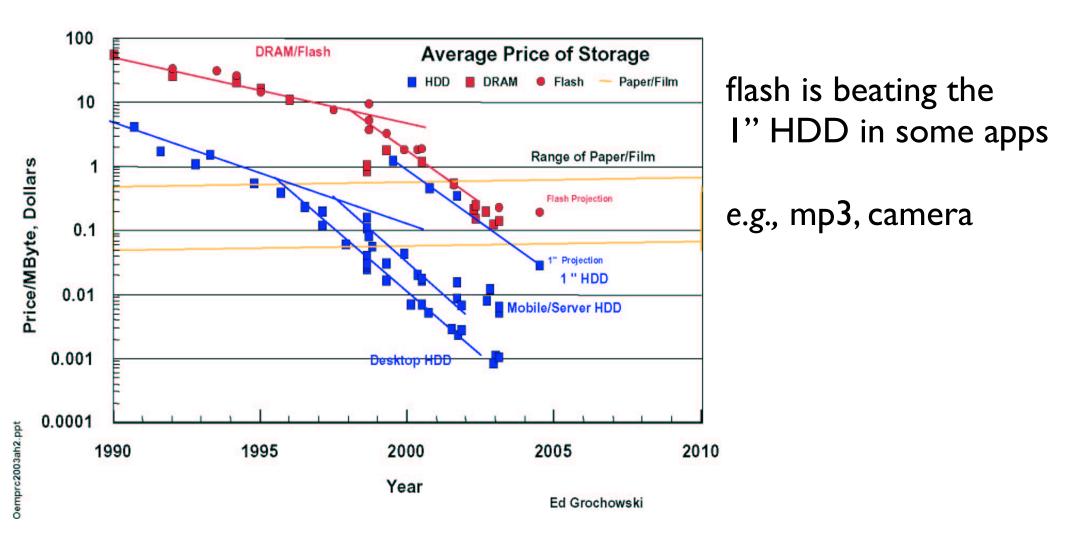
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Cell density	Low	High	High	Medium	Medium/high	Medium/high
Nonvolatility	No	No	Yes	Yes	Yes	Yes
Endurance	Infinite	Infinite	Limited	Limited	Infinite	Infinite
Cell leakage	Increasing	High	Low	Low	Low	Low
Low voltage	Yes	Limited	Limited	Limited	Yes	Yes
Complexity	Low	Medium	Medium	Medium	Medium	Medium

## price is our real advantage.

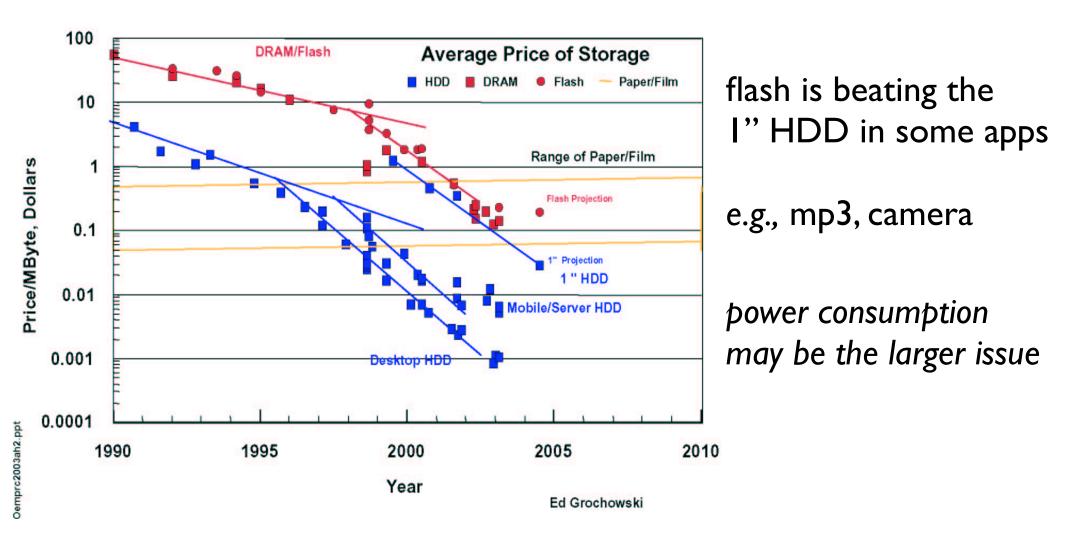


### price is our real advantage.



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### price is our real advantage.



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#### power consumption is not an advantage

#### latency ...

#### fundamental limits of magnetism?

#### power consumption is not an advantage

latency ...

#### fundamental limits of magnetism?

more importantly ...

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#### power consumption is not an advantage

latency ...

#### fundamental limits of magnetism?

#### more importantly ... will we get "scooped" like bubbles?

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# SO!

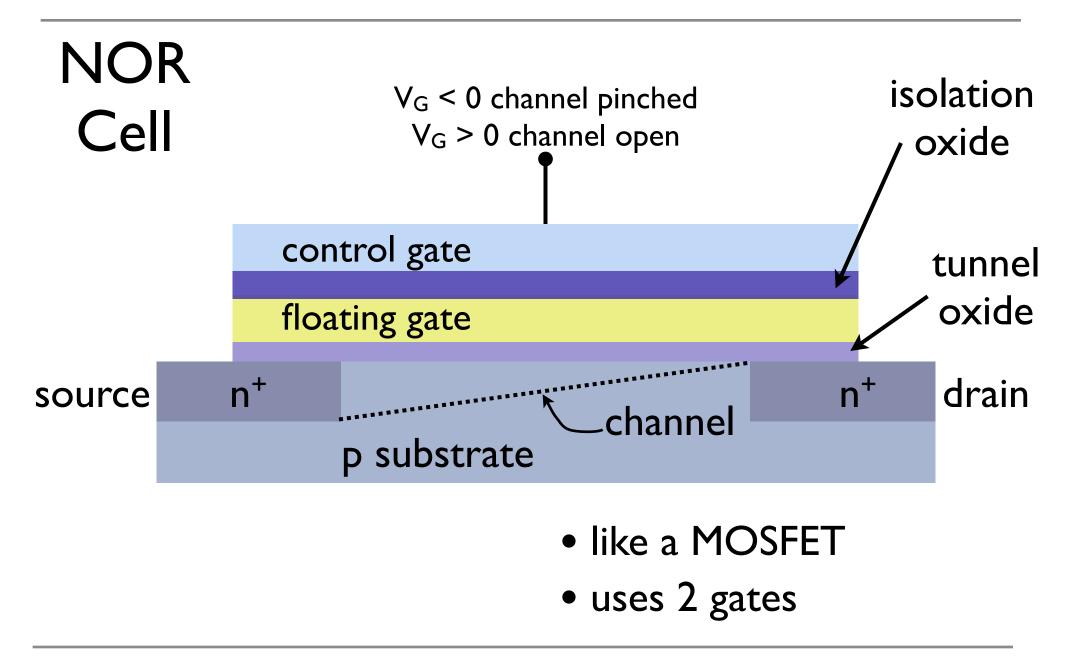
#### before we get into alternatives ...

how does what we have work?

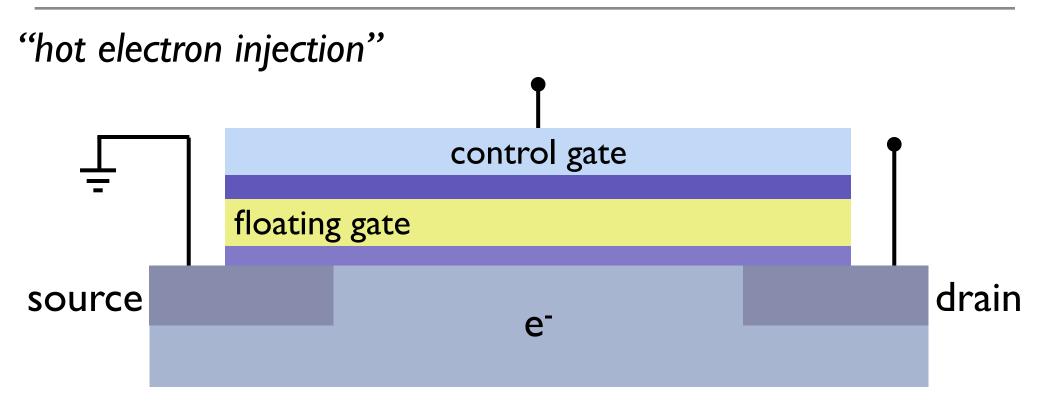
# SO!

before we get into magnetic recording details ...

how does flash work?

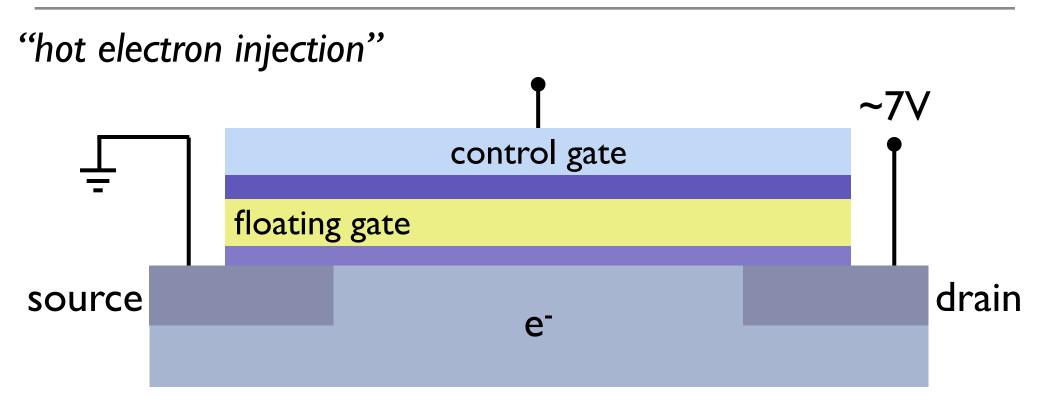


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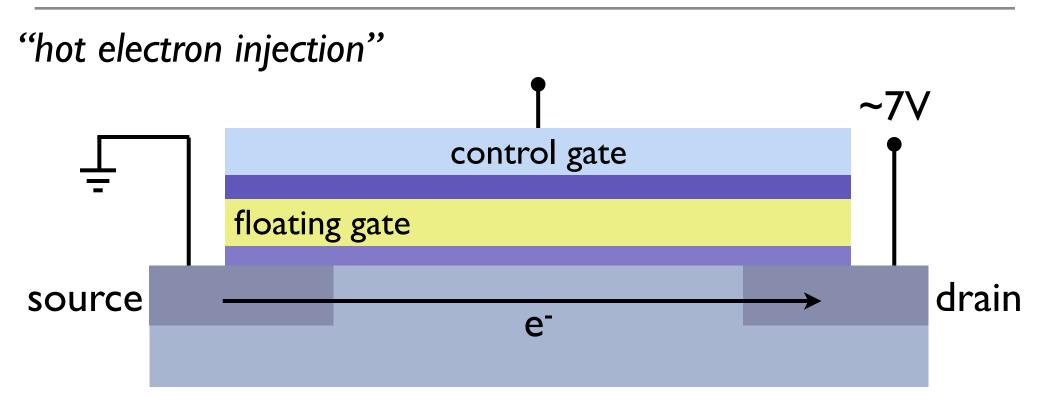
• ~7V to drain

- ~I2V to control gate / open channel injects e<sup>-</sup> into floating gate through tunnel oxide
- floating gate now charged



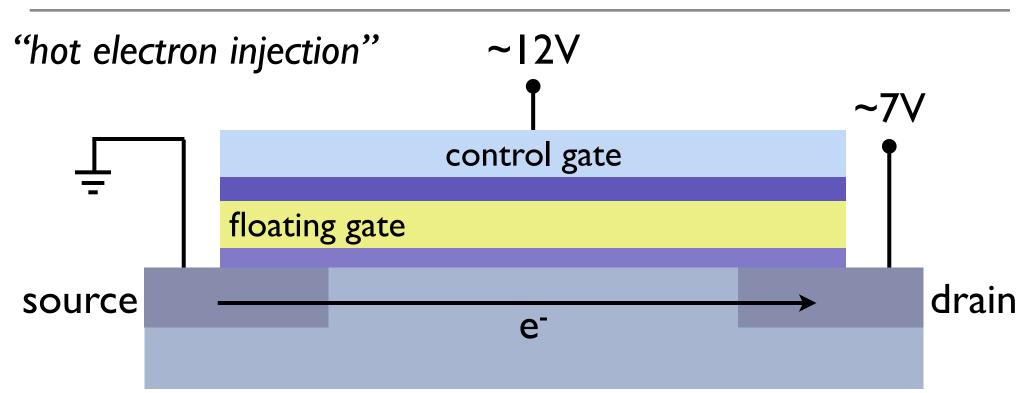
• ~7V to drain

- ~I2V to control gate / open channel injects e<sup>-</sup> into floating gate through tunnel oxide
- floating gate now charged



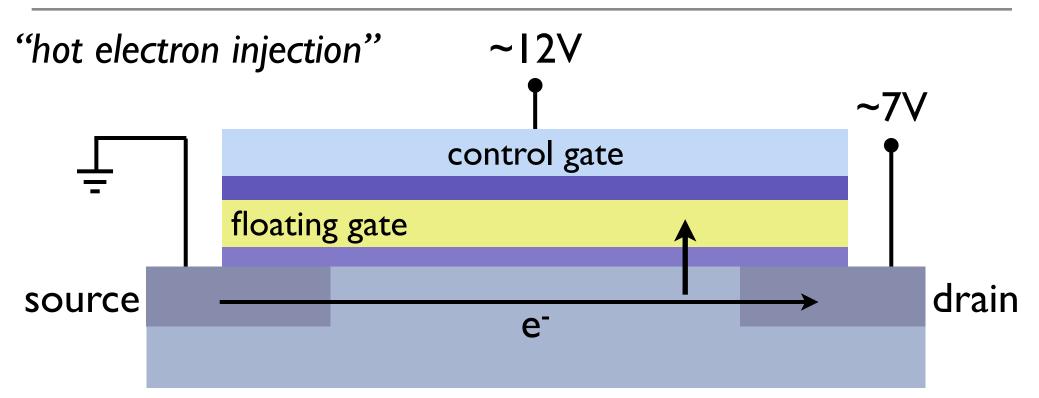
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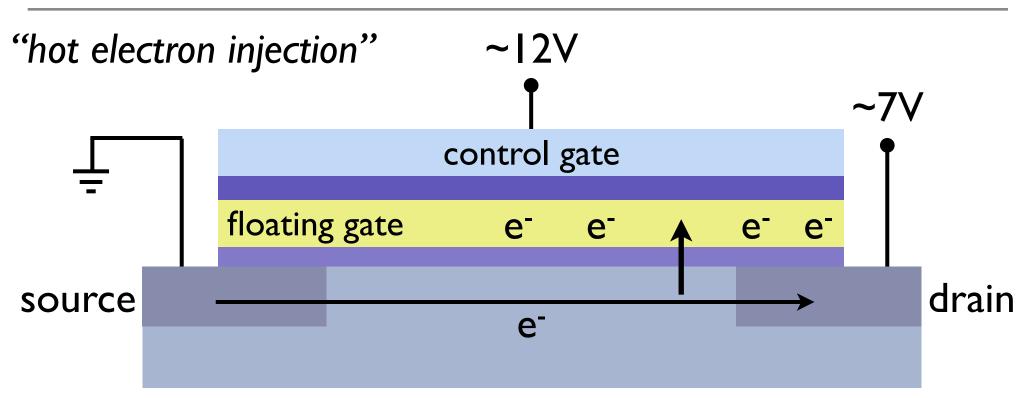
• ~7V to drain

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• ~7V to drain

- ~I2V to control gate / open channel injects e<sup>-</sup> into floating gate through tunnel oxide
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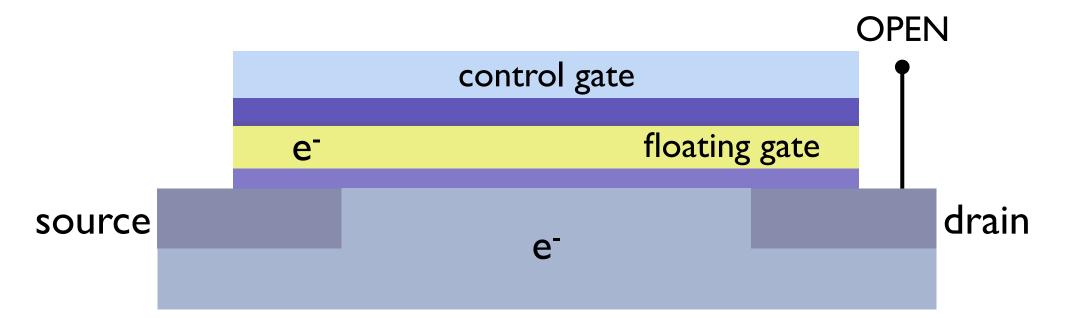


• ~7V to drain

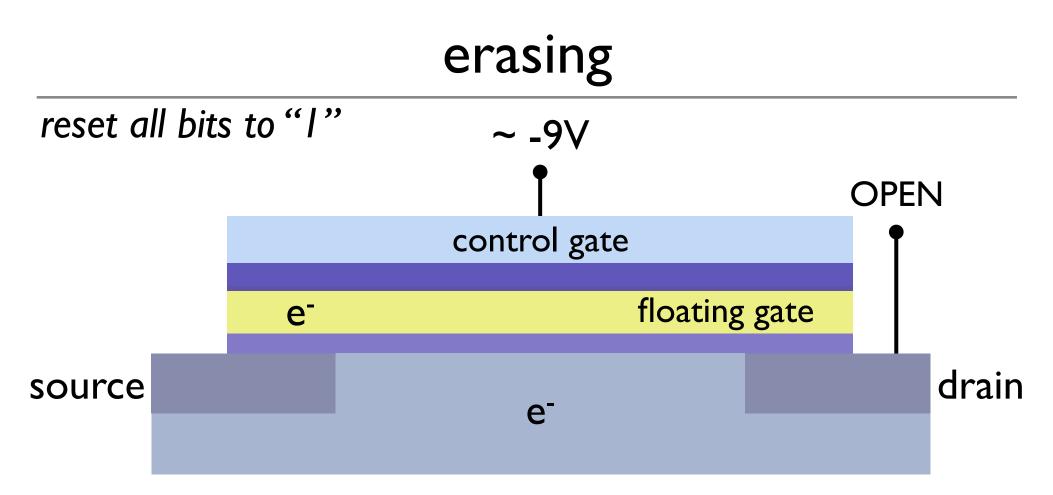
- ~I2V to control gate / open channel injects e<sup>-</sup> into floating gate through tunnel oxide
- floating gate now charged

### erasing

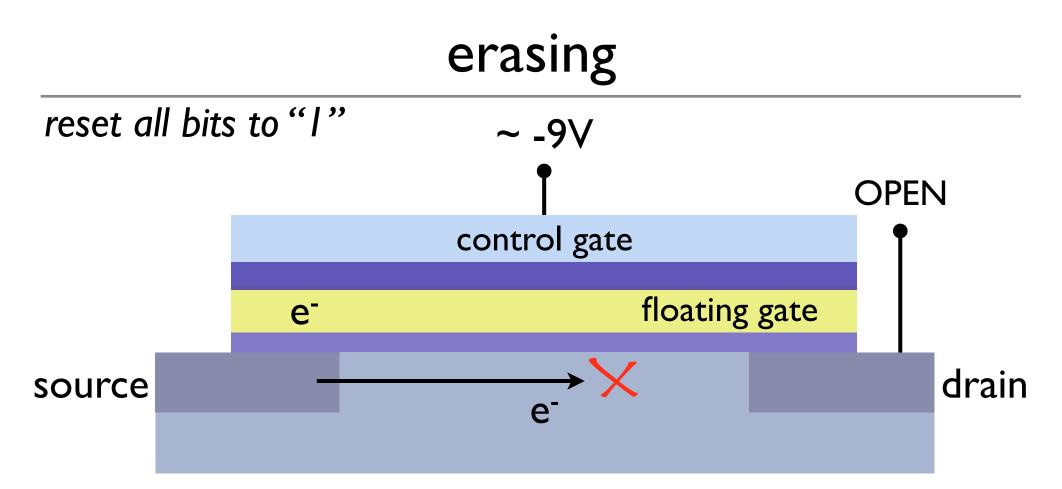
reset all bits to "I"



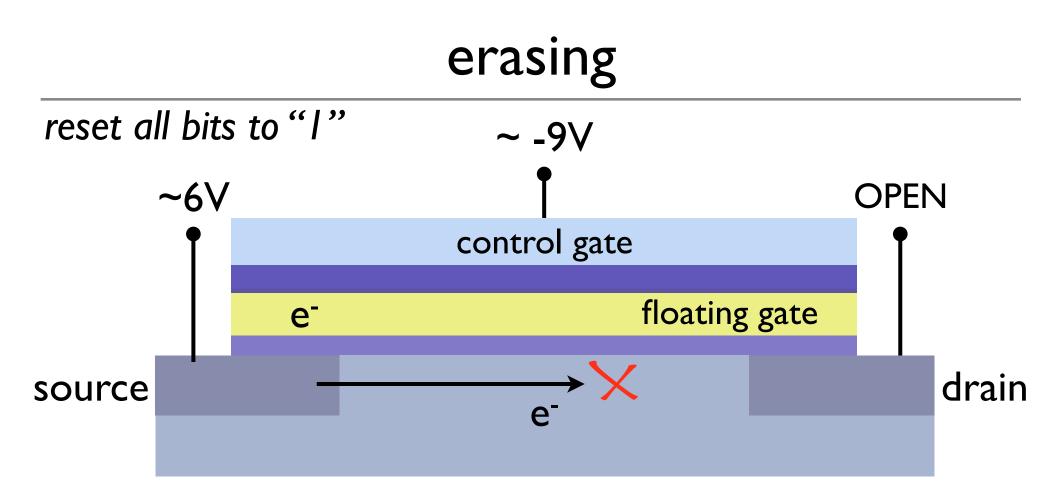
- -9V to control
  - pinch off channel
- ~6V to source
- suck electrons out of floating gate into source Fowler-Nordheim tunneling



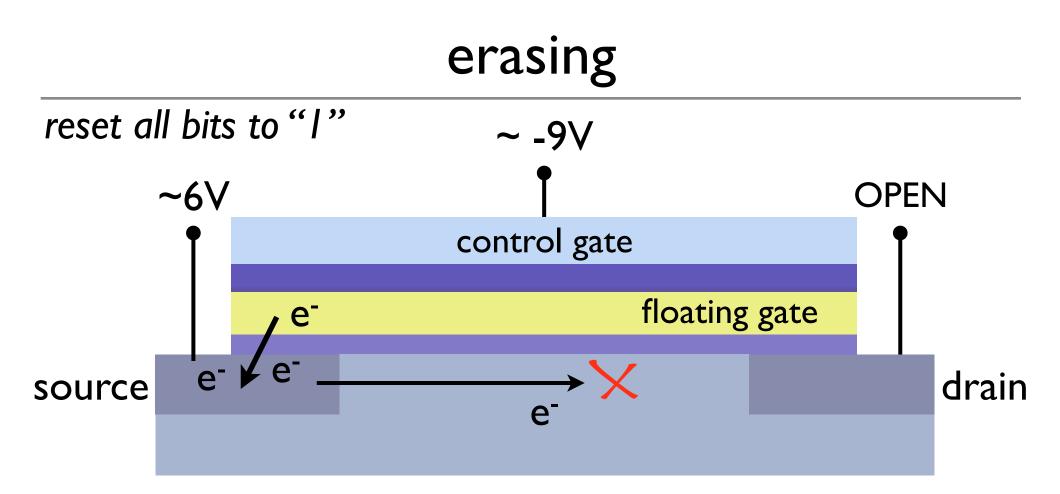
- -9V to control
  - pinch off channel
- ~6V to source
- suck electrons out of floating gate into source Fowler-Nordheim tunneling



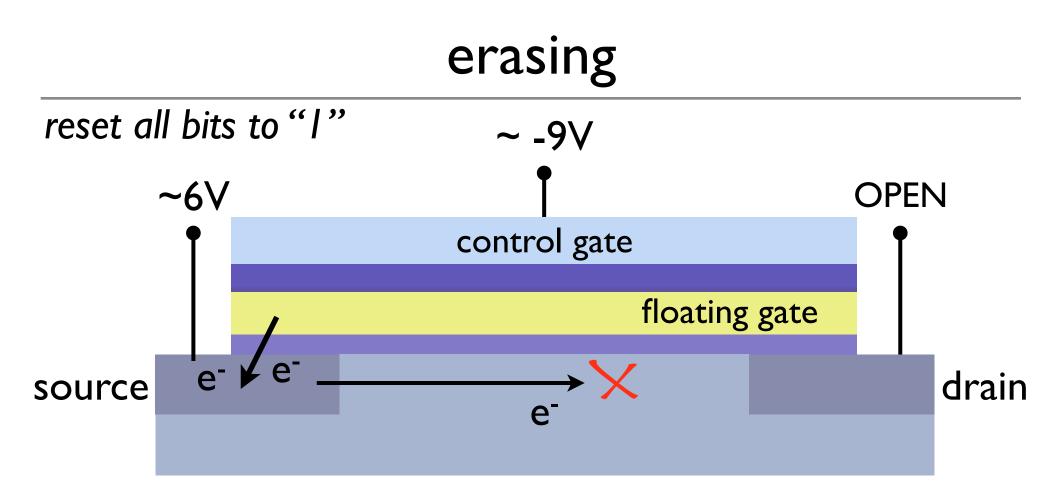
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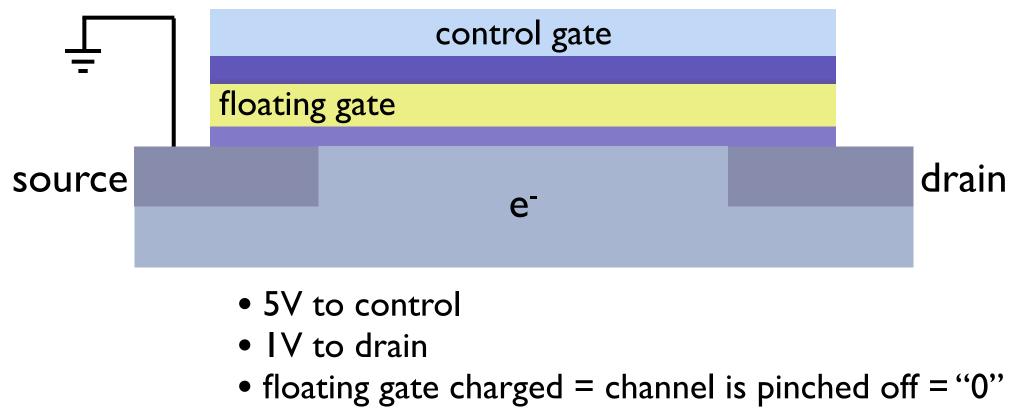


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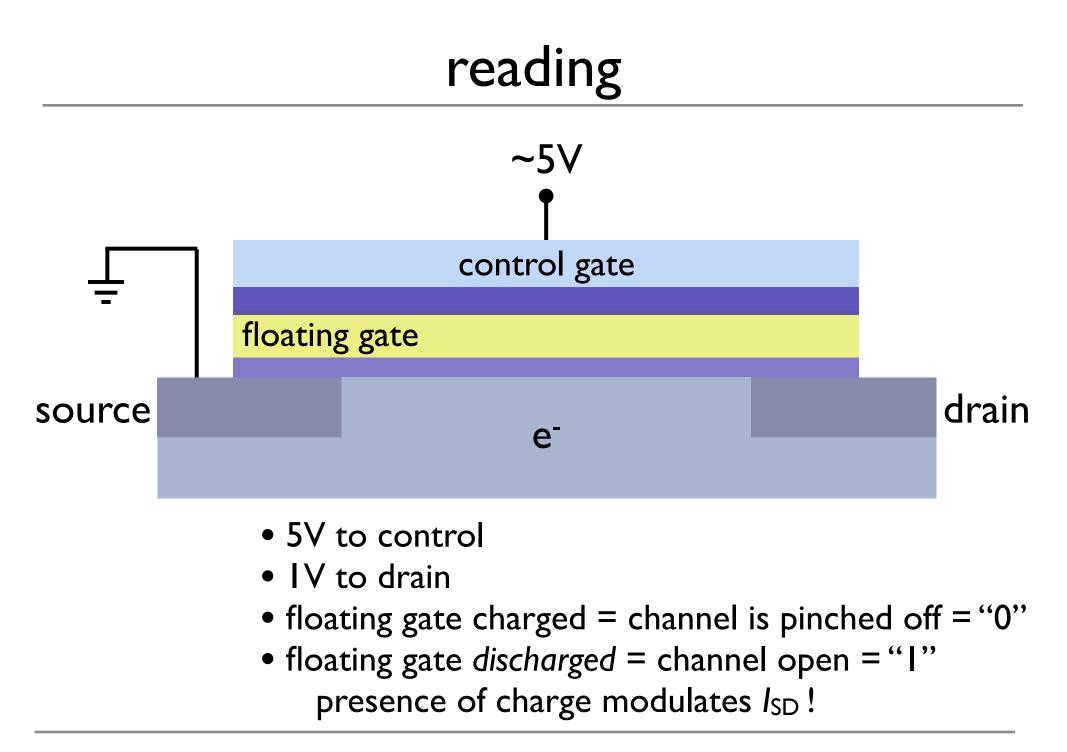


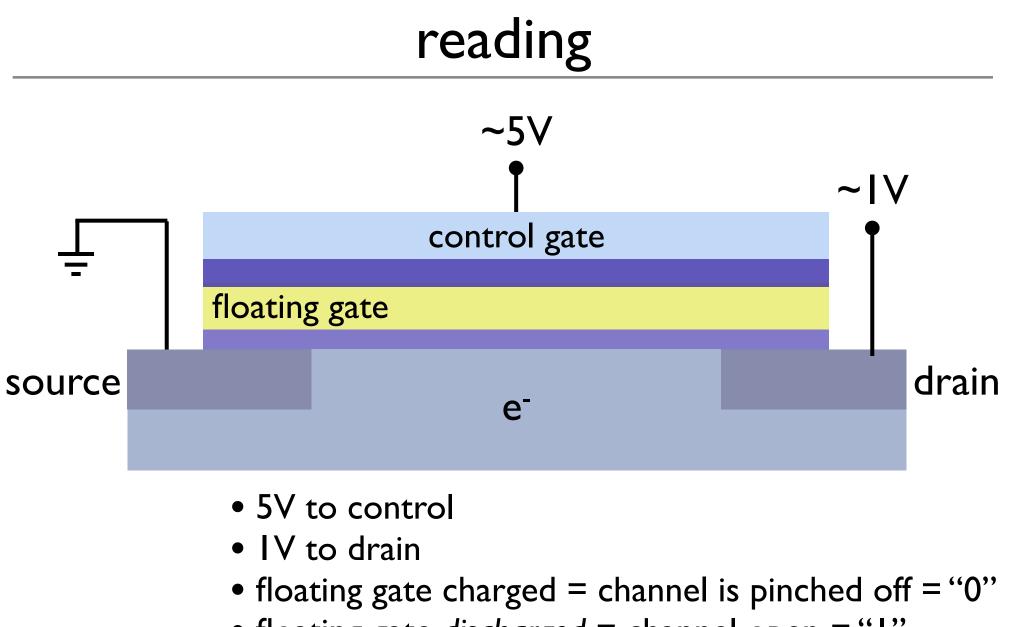
- ~6V to source
- suck electrons out of floating gate into source Fowler-Nordheim tunneling

# reading

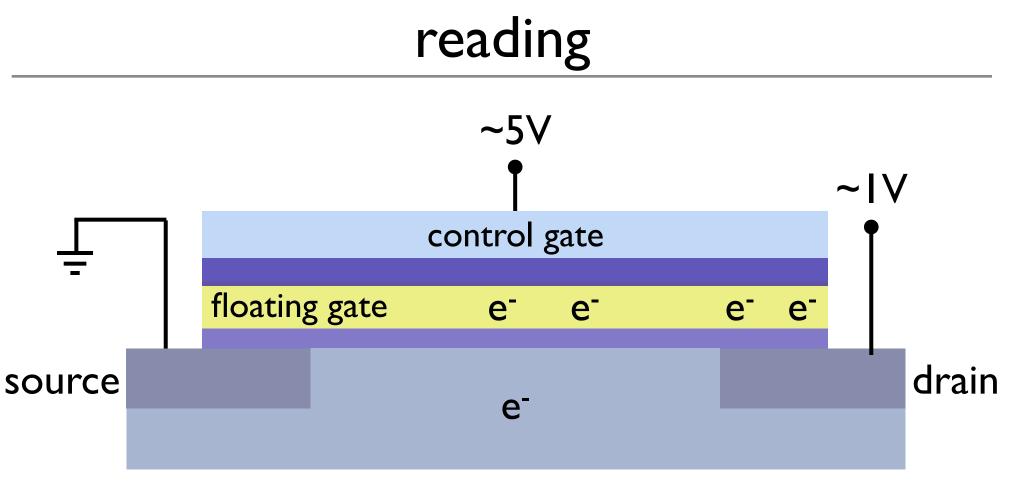


 floating gate discharged = channel open = "I" presence of charge modulates I<sub>SD</sub> !





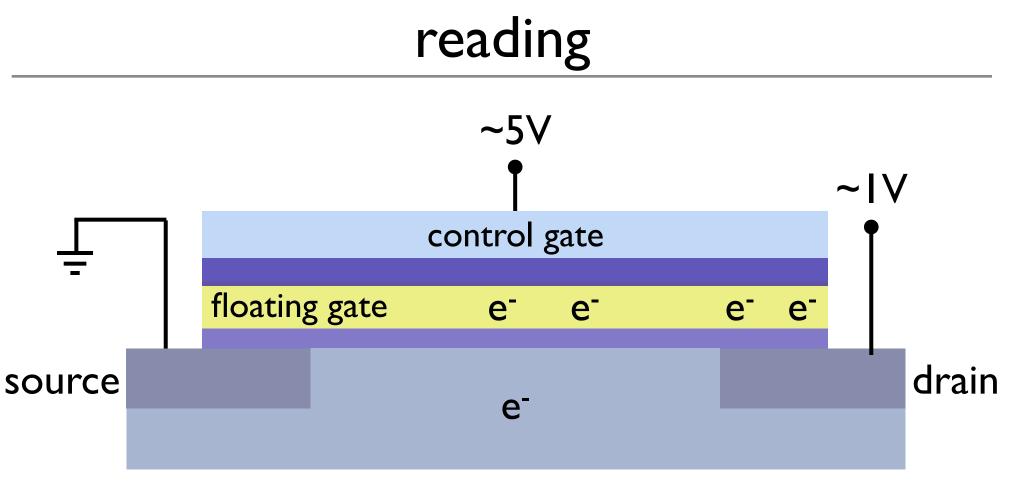
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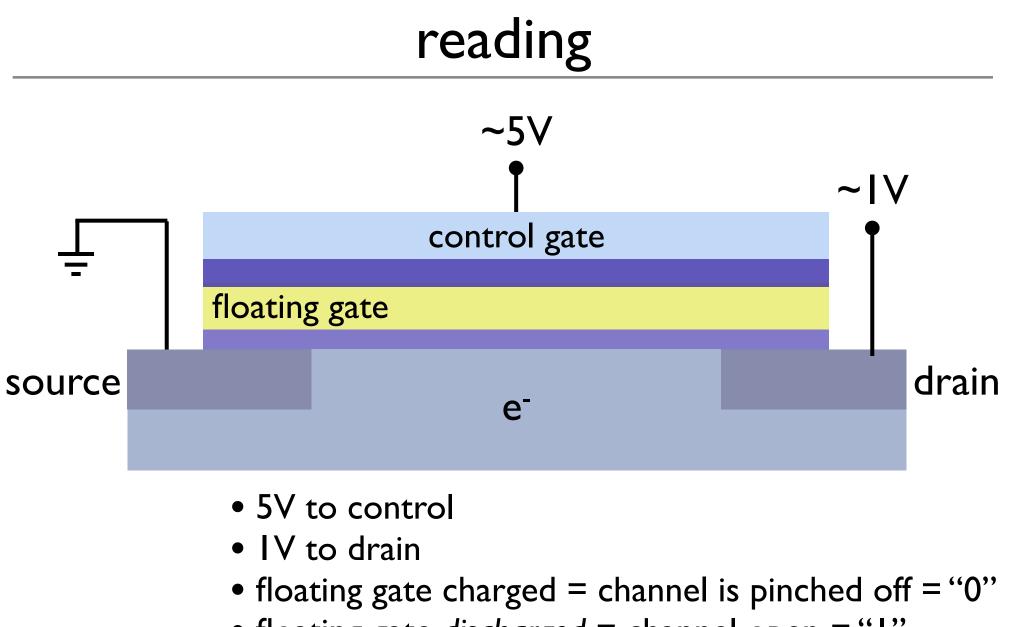
- 5V to control
- IV to drain
- floating gate charged = channel is pinched off = "0"
- floating gate discharged = channel open = "I" presence of charge modulates I<sub>SD</sub> !

#### reading ~5V ~IV control gate floating gate e<sup>-</sup> e<sup>-</sup> e<sup>-</sup> e<sup>-</sup> drain source

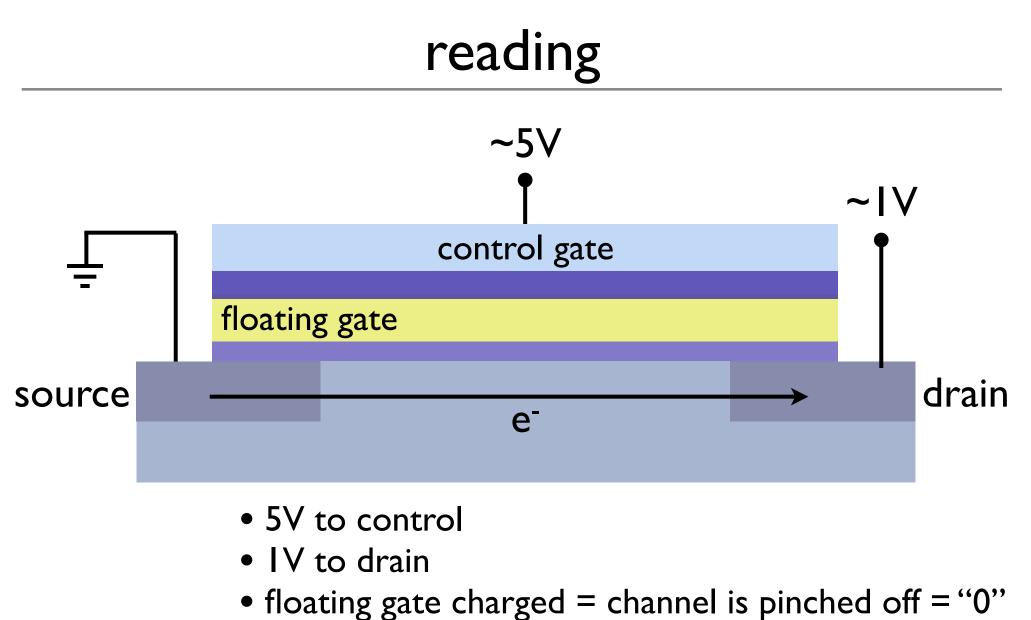
- 5V to control
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- 5V to control
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- floating gate charged = channel is pinched off = "0"
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 floating gate discharged = channel open = "I" presence of charge modulates I<sub>SD</sub> !



 floating gate discharged = channel open = "I" presence of charge modulates I<sub>SD</sub> !

- no mechanical limitations
- Iower latency
  - = attractive for speed, noise, power consumption, reliability.

- lower latency
  - = attractive for speed, noise, power consumption, reliability.
  - cost/GB still significantly higher (but decreasing rapidly!)
  - finite number of erase/write (typically 10<sup>6</sup> cycles guaranteed) unable to support an OS (swap!)
     warranties on flash-based disks trending HDD

## the basics of phase change memory

#### this is your homework ...

in 3 pages:

#### how does phase-change memory work? advantages and disadvantages? could it be disruptive? who are the major players?

places to start:

G.A. Gibson et al, Appl. Phys. Lett. 86, 051902 (2005) http://domino.research.ibm.com/comm/pr.nsf/pages/news.20061211\_phasechange.html

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### Transcript

#### http://bama.ua.edu/~pleclair/PH587/

#### PDF version of these slides

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